Ultra-Fast Silicon Detector

- The "4D" challenge
- A parameterization of time resolution
- The "Low Gain Avalanche Detectors" project
- Laboratory measurements
- UFSD: LGAD optimized for timing measurements
- WeightField2: a simulation program to optimize UFSD
- First measurements
- Future directions

Nicolo Cartiglia

With
INFN Gruppo V, LGAD group of RD50, FBK and Trento University, Micro-Electronics Turin group
Rome2 - INFN.

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Ministero degli Affari Esteri
e della Cooperazione Internazionale

DIREZIONE GENERALE
PER LA PROMOZIONE DEL SISTEMA PAESE
Unità per la cooperazione scientifica
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The **4D** challenge

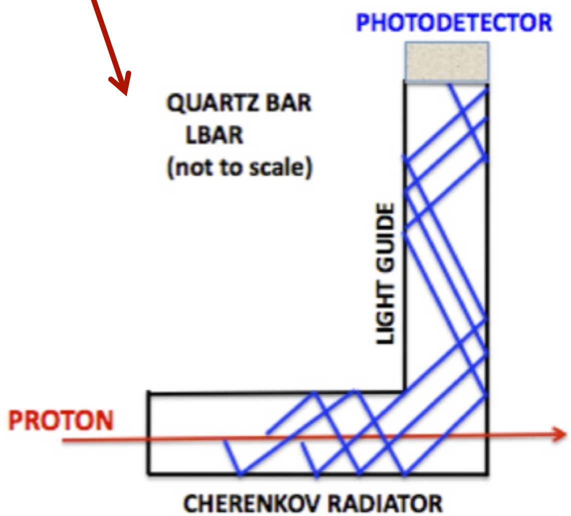
Is it possible to build a detector with concurrent excellent time and position resolution?

Can we provide in the same detector and readout chain:

- **Ultra-fast timing resolution [~ 10 ps]**
- **Precision location information [10's of μm]**

State-of-the-art Timing Detectors

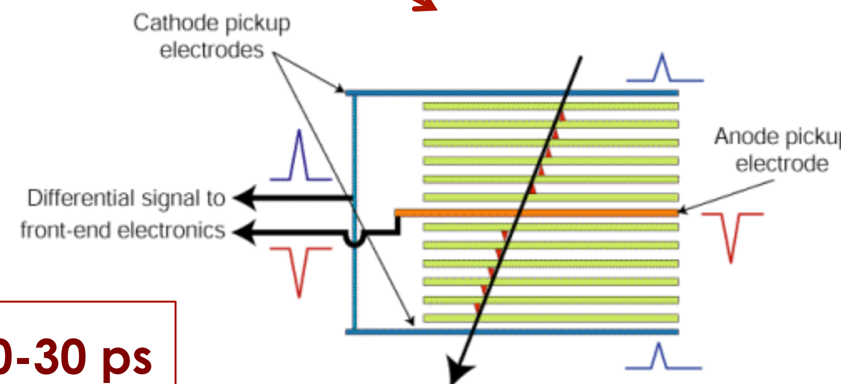
Timing detectors exploit very fast physics processes such as **Cherenkov light** emission or **electronic avalanches** to create prompt signals



CMS/ATLAS

σ_t **~ 20-30 ps**

σ_x **~ 1-2 mm**

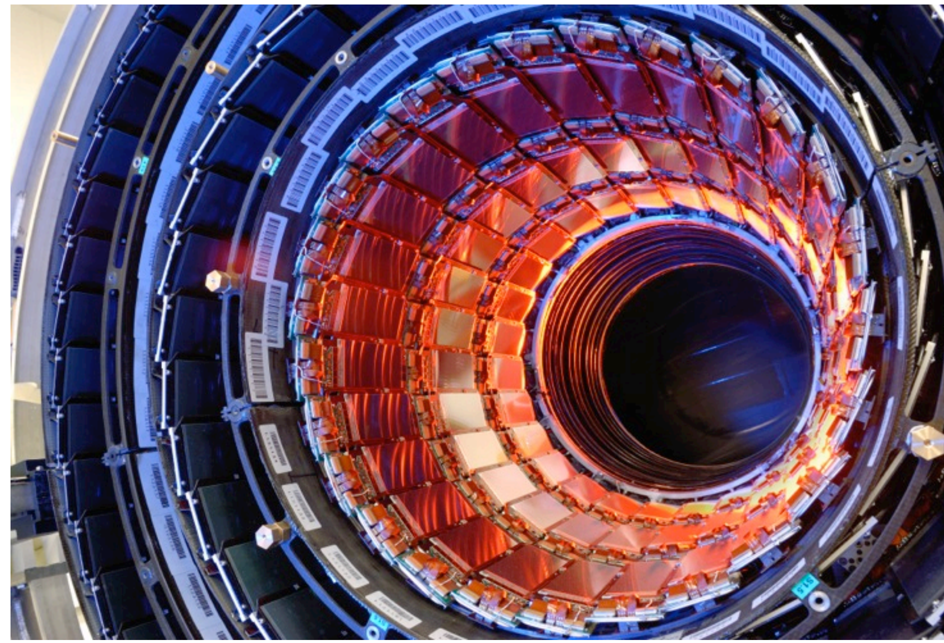


ALICE

- These detectors measure time very accurately but locate particles with the **precision of ~ 1 mm**
- Good timing is obtain by using a gain mechanism, either in the detector or in the electronics

State-of-the-art Position Detectors

Extremely good position detectors are currently in use in every major high energy physics experiment:



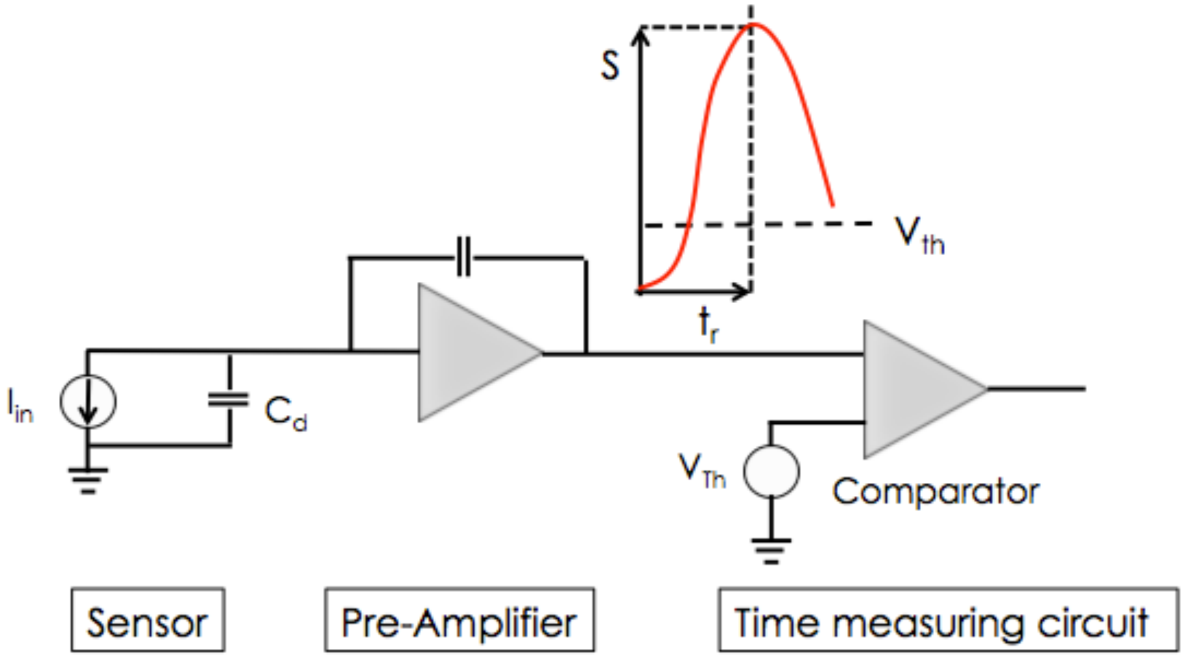
- Millions of channels
- Very reliable
- Very radiation hard

The timing capability is however limited to ~ 100-150 ps
(NA62 @CERN)

σ_t ~ 100-150 ps
σ_x ~ 20-30 μm

A time-tagging detector

(a simplified view)



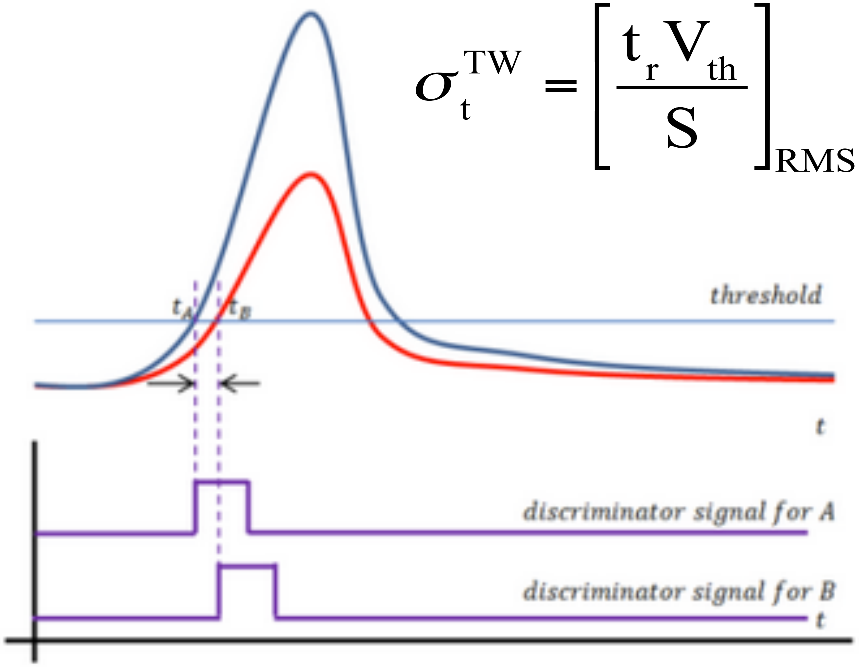
Time is set when the signal crosses the comparator threshold

The timing capabilities are determined by the characteristics of the signal at the output of the pre-Amplifier and by the TDC binning.

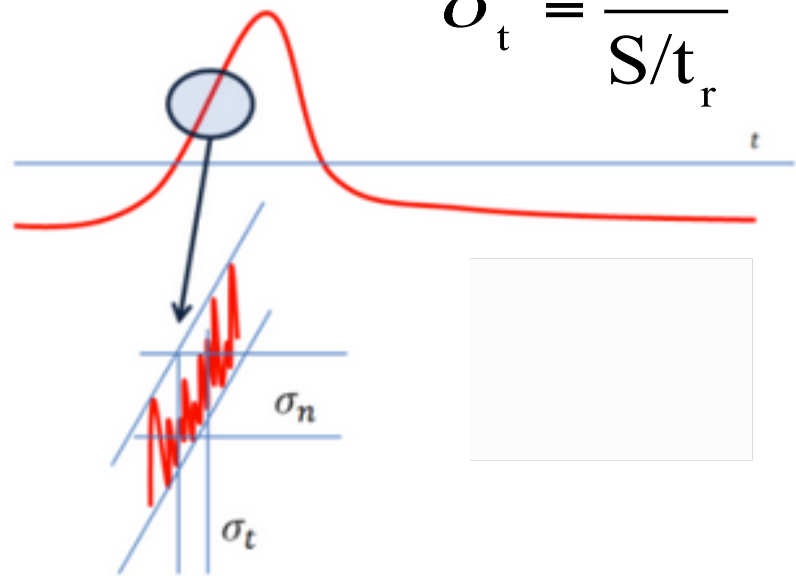
Noise source: Time walk and Time jitter

Time walk: the voltage value V_{th} is reached at different times by signals of different amplitude

Jitter: the noise is summed to the signal, causing amplitude variations



$$\sigma_t^{TW} = \left[\frac{t_r V_{th}}{S}\right]_{RMS}$$



$$\sigma_t^{J} = \frac{N}{S/t_r}$$

Due to the physics of signal formation

Mostly due to electronic noise

$$\sigma_{Total}^2 = \sigma^2_{Time\ Walk} + \sigma_{Jitter}^2 + \sigma_{TDC}^2$$

Time Resolution and slew rate

Using the expressions in the previous page, we can write

$$\sigma_t^2 = \left(\left[\frac{V_{th}}{S/t_r}\right]_{RMS}\right)^2 + \left(\frac{N}{S/t_r}\right)^2 + \left(\frac{TDC_{bin}}{\sqrt{12}}\right)^2$$

Time Walk | Jitter | JTDC

where:

- S/t_r = dV/dt = slew rate
- N = system noise
- V_{th} = 10 N

Assuming constant noise, to minimize time resolution **we need to maximize the S/t_r term** (i.e. the slew rate dV/dt of the signal)

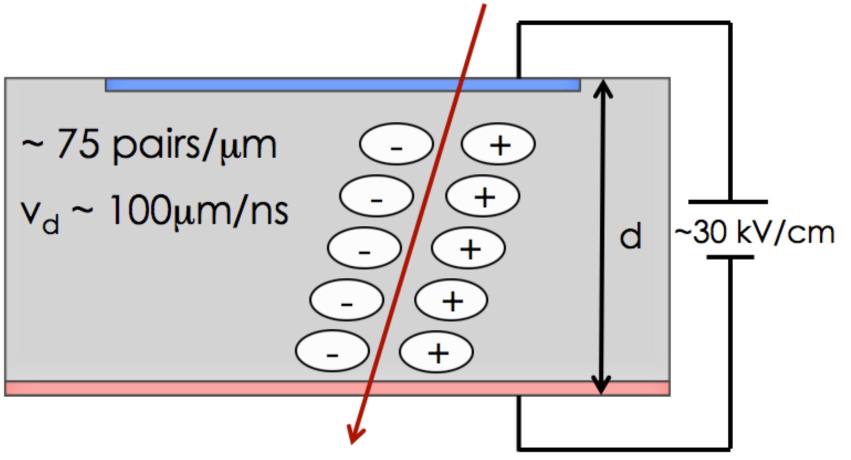
➔ We need large and short signals ➔

Signal formation in silicon detectors

We know we need a large signal, but **how is the signal formed?**

What is controlling the slew rate?

$$\frac{dV}{dt} \propto ?$$



A particle creates charges, then:

- The charges start moving under the influence of an external field
- The motion of the charges induces a current on the electrodes
- The signal ends when the charges reach the electrodes

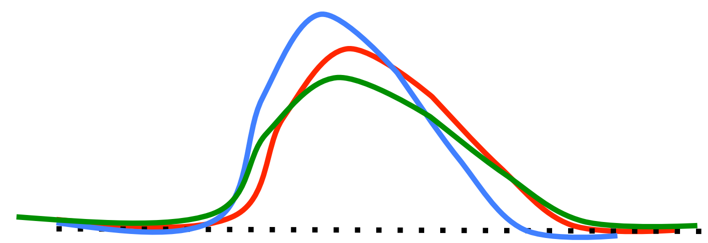
How to make a **good** signal

Signal shape is determined by Ramo's Theorem:

$$i \propto q v E_w$$

Drift velocity

Weighting field



A key to good timing is the uniformity of signals:

Drift velocity and **Weighting field** need to be **as uniform as possible**

Good signals for Timing

Velocity:

$$i \propto q v E_w$$

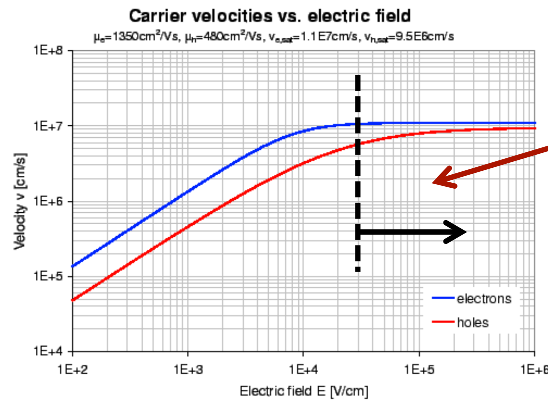
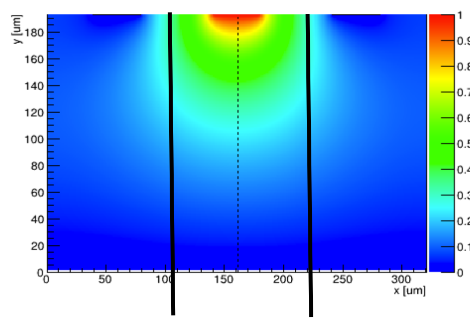


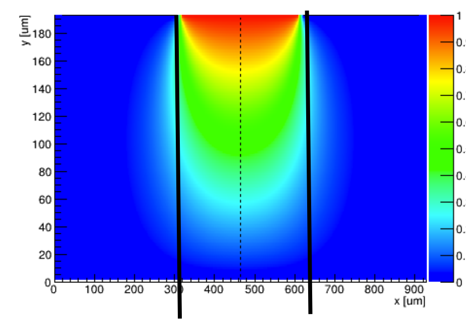
Figure: Electron and hole velocities vs. the electric field strength in silicon.

We want to operate in this regime: saturated velocity

Weighting field:

$$i \propto q v E_w$$





Best: uniform weighting field in a pitch

Charge:

$$i \propto q v E_w$$

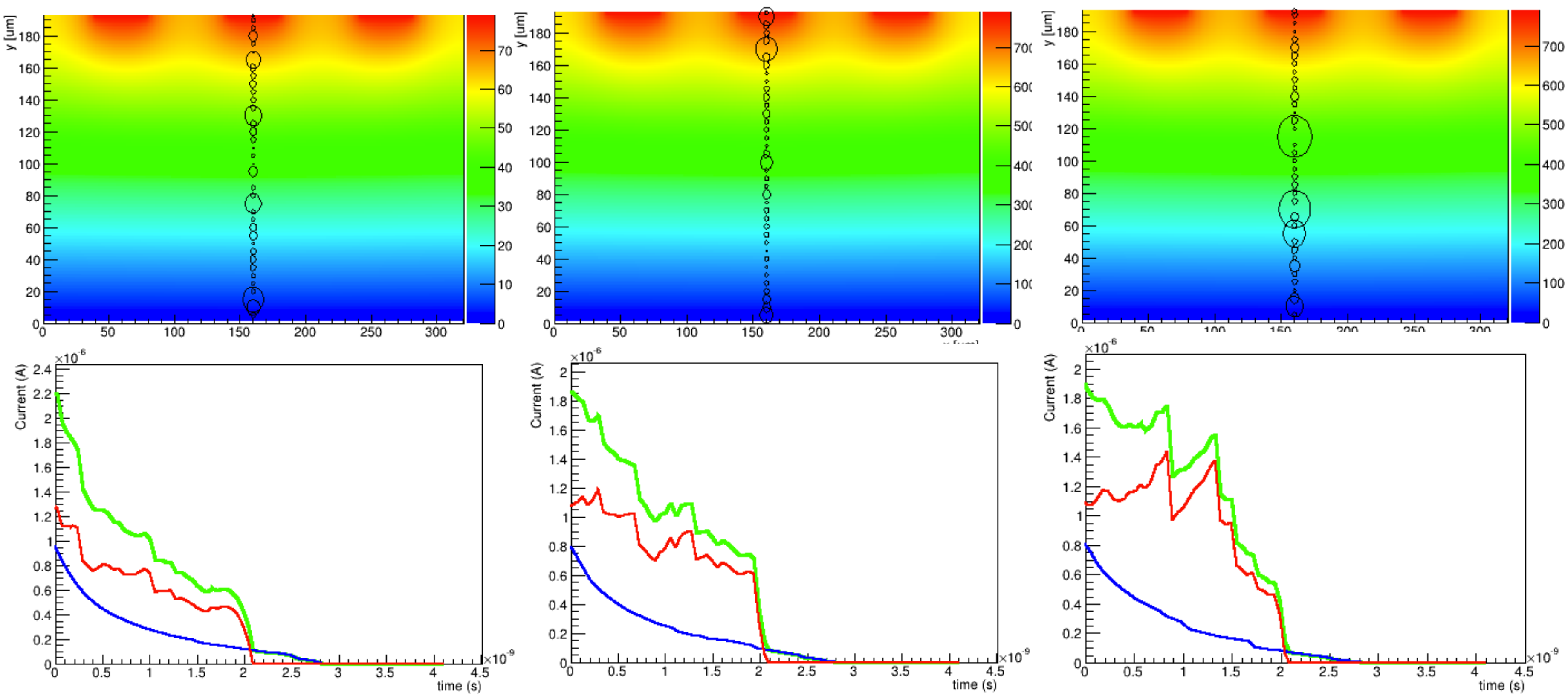
- ➔ Highest possible E field to saturate velocity
- ➔ Large pad to have uniform weighting field
- ➔ Lot's of charge

Non-Uniform Energy deposition

Landau Fluctuations cause two major effects:

- Amplitude variations, that can be corrected with time walk compensation
- For a given amplitude, the charge deposition is non uniform.

These are 3 examples of this effect:



What is the signal of one e/h pair?

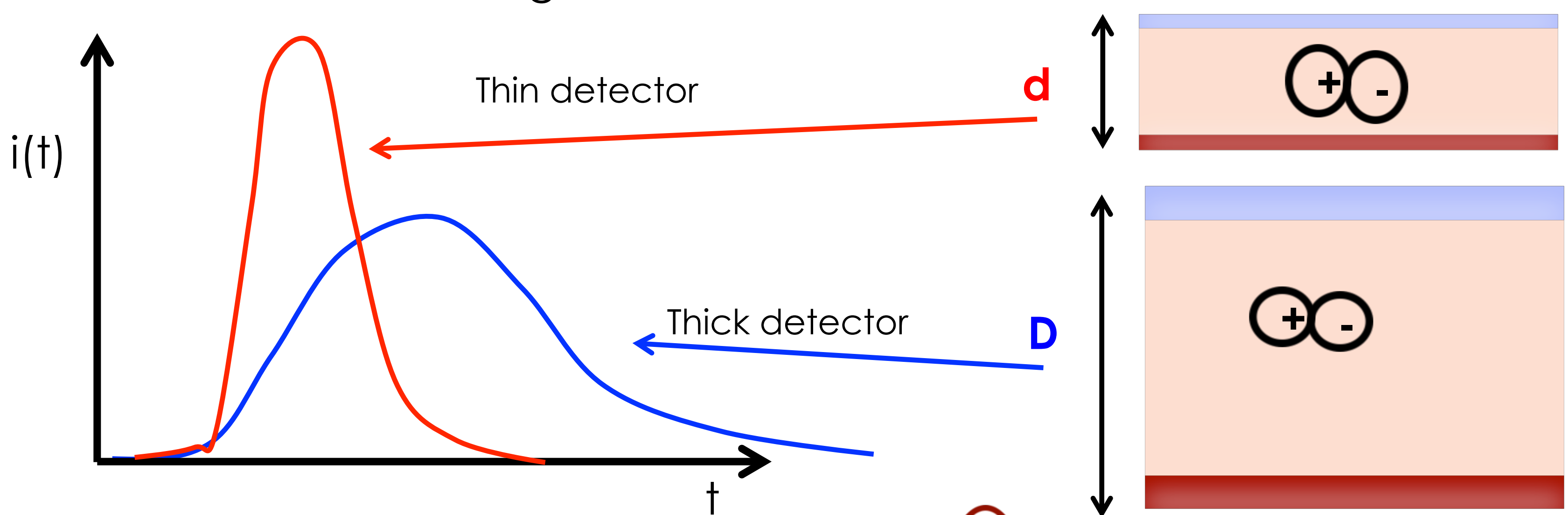
(Simplified model for pad detectors)

Let's consider **one single electron-hole pair.**

The integral of their currents is equal to the electric charge, q:

$$\int [i_{el}(t) + i_h(t)]dt = q$$

However **the shape of the signal depends on the thickness** d:
thinner detectors have higher slew rate



➔ One e/h pair generates higher current in thin detectors

$$i \propto qv\frac{1}{d}$$

Weighting field

Large signals from thick detectors?

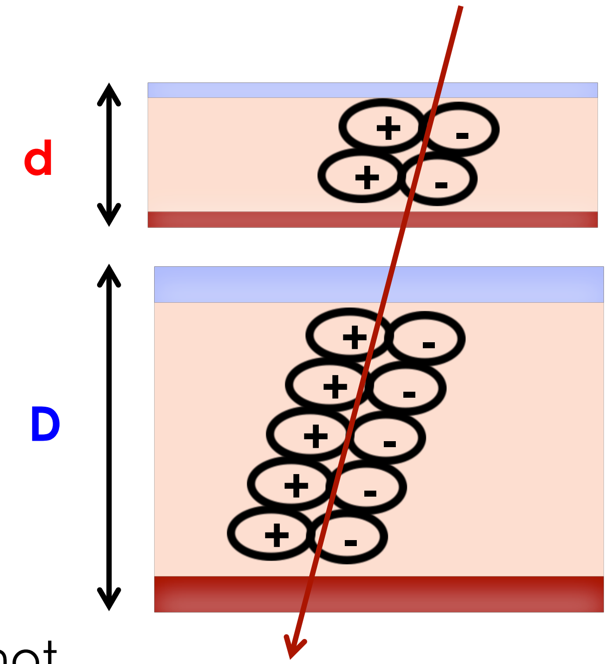
(Simplified model for pad detectors)

Thick detectors have higher number of charges:

$$Q_{tot} \sim 75\ q*d$$

However each charge contributes to the initial current as:

$$i \propto qv\frac{1}{d}$$



The initial current for a silicon detector does not depend on how thick (d) the sensor is:

$$i = Nq\frac{k}{d}v = (75\cancel{d}q)\frac{k}{\cancel{d}}v = 75kqv \sim 1-2*10^{-6}A$$

Number of e/h = 75/micron

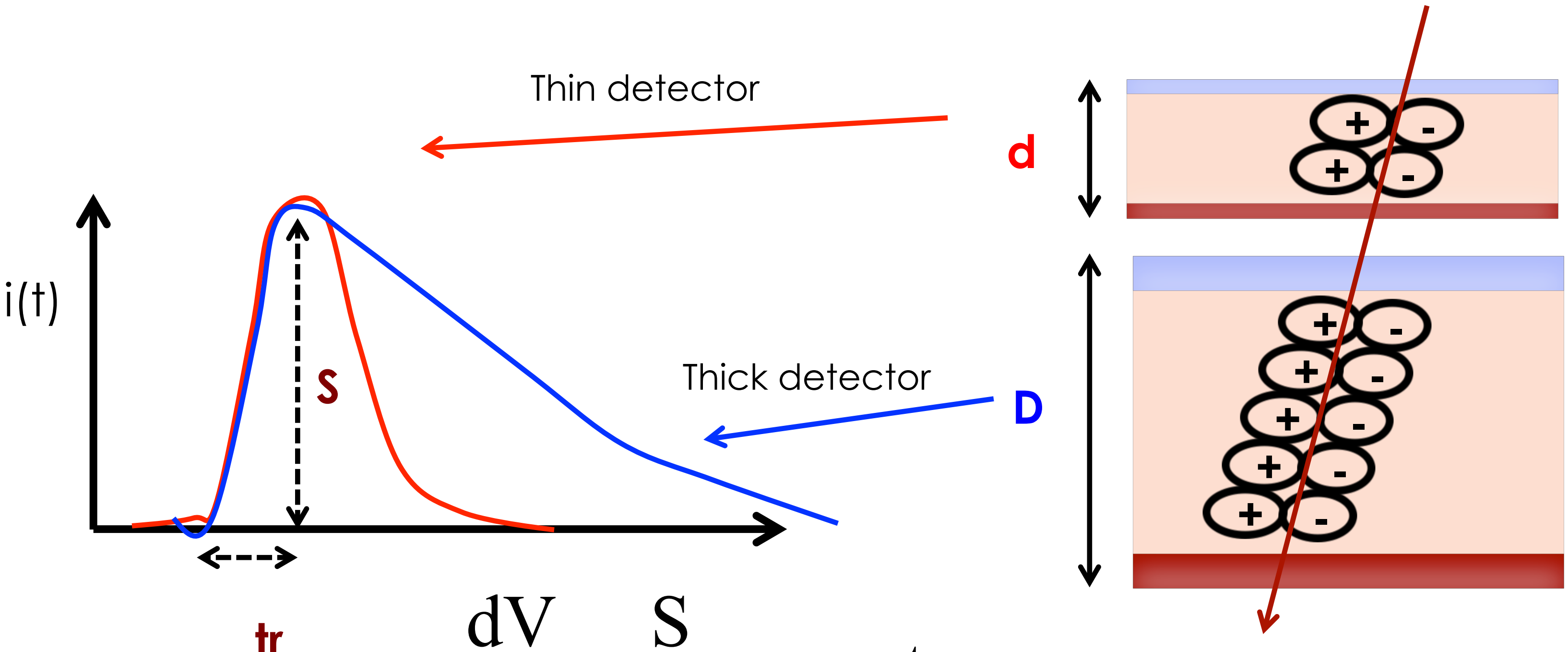
Weighting field

velocity

→ Initial current = constant

Thin vs Thick detectors

(Simplified model for pad detectors)



$$\frac{dV}{dt} \sim \frac{S}{t_r} \sim \text{const}$$

Thick detectors have longer signals, not higher signals

Best result : NA62, 150 ps on a 300 x 300 micron pixels

How can we do better?

Possible approaches

We need to minimize this expression:

$$\sigma_t^2 = ([\frac{V_{th}}{S/t_r}]_{RMS})^2 + (\frac{N}{S/t_r})^2$$

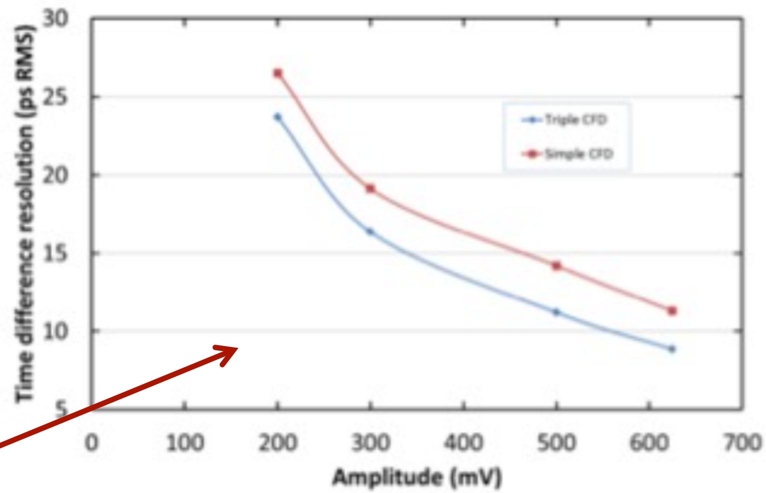
- **APD** (silicon with gain ~ 100): maximize S
  - Very large signal

- **Diamond:** minimize N, minimize t_r
  - Large energy gap, very low noise, low capacitance
  - Very good mobility, short collection time t_r

- **LGAD** (silicon with gain ~ 10): minimize N, moderate S
  - Low gain to avoid shot noise and excess noise factor

The APD approach

The key to this approach is the large signal: if your signal is large enough, everything becomes easy.



So far they reported:

- Excellent time resolution
- Good radiation resistance up to < 10^{14} neq/cm^2
- They will propose a system for the CT-PPS

See:

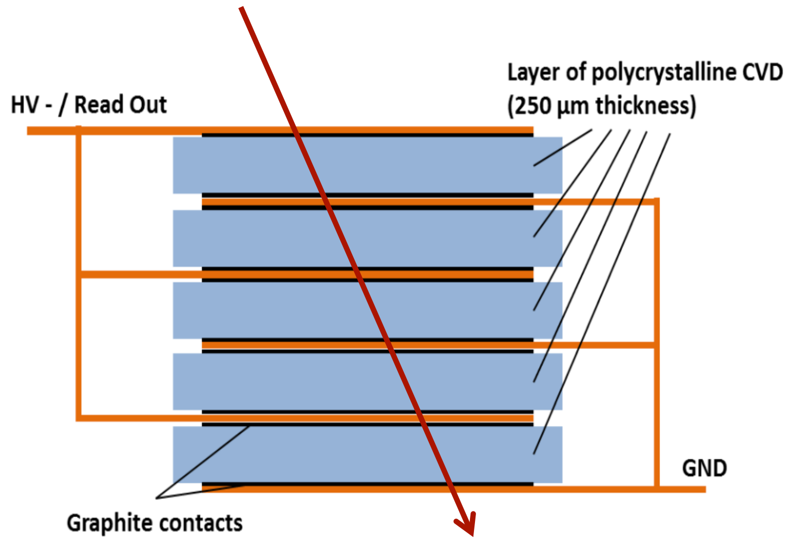
https://indico.cern.ch/event/363665/contribution/7/material/slides/0.pdf

The Diamond approach

Diamond detectors have small signal: two ways of fighting this problem

1) Multilayer stack

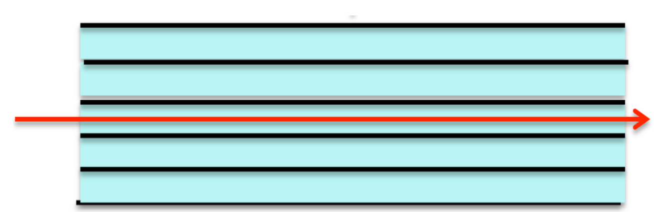
The signal is increased by the sum of many layers while it keeps very short rise time



Best resolution: ~ 100 ps

2) Grazing

The particle crosses the diamond sensor along the longitudinal direction



The "Low-Gain Avalanche Detector" approach

Is it possible to manufacture a silicon detector that looks like a normal pixel or strip sensor, but with a much larger signal (RD50)?

- 750 e/h pair per micron instead of 75 e/h?
- Finely Segmented
- Radiation hard
- No dead time
- Very low noise (low shot noise)
- No cross talk
- Insensitive to single, low-energy photon

Many applications:

- Low material budget (signal in 30 micron == signal 300 micron)
- Excellent immunity to charge trapping (larger signal, shorter drift path)
- Very good S/N: 5-10 times better than current detectors
- Good timing capability (large signal, short drift time)

Gain in Silicon detectors

Gain in silicon detectors is commonly achieved in several types of sensors. It's based on the avalanche mechanism that starts in high electric fields: **E ~ 300 kV/cm**

Charge multiplication

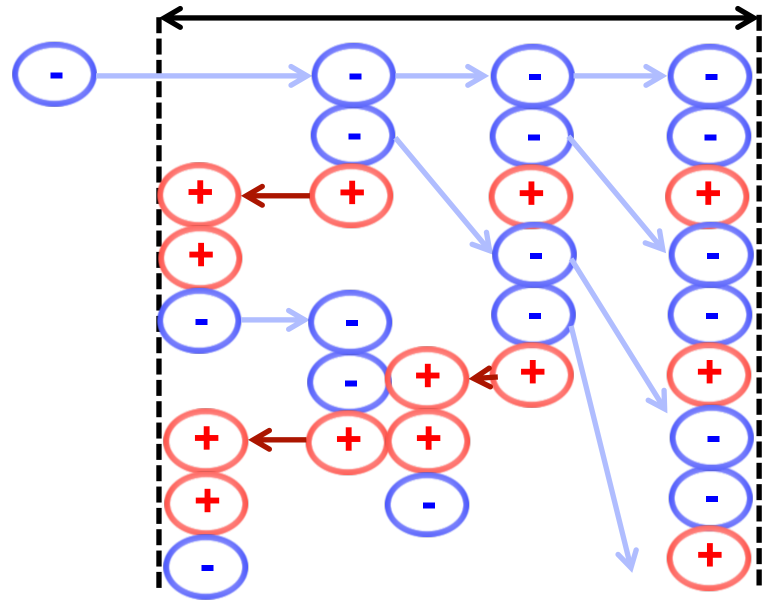
$$N(l) = N_0 \cdot e^{\alpha \cdot l}$$

Gain:

$$G = e^{\alpha\, l}$$

$$\alpha_{e,h}(E) = \alpha_{e,h}(\infty) * \exp\left(-\frac{b_{e,h}}{|E|}\right)$$

α = strong E dependance
α ~ 0.7 pair/μm for electrons,
α ~ 0.1 for holes



Concurrent multiplication of electrons and holes generate very high gain

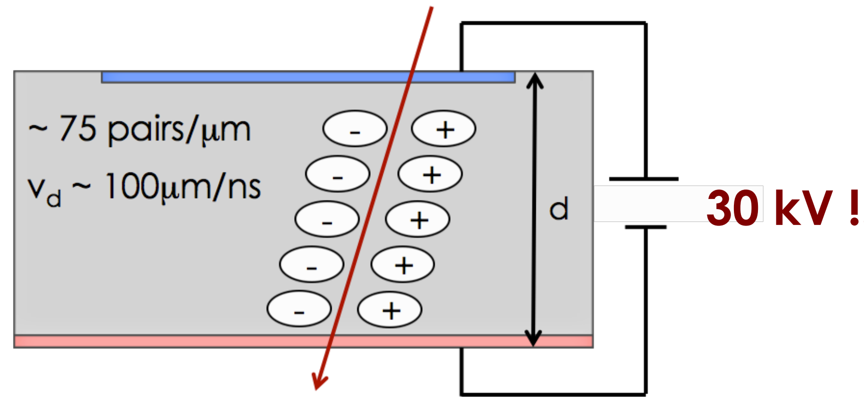
Silicon devices with gain:

- **APD: gain 50-500**
- **SiPM: gain ~ 10^4**

How can we achieve E ~ 300kV/cm?

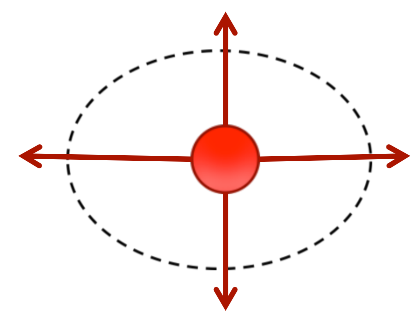
1) Use external bias: assuming a 300 micron silicon detector, we need V_{bias} **= 30 kV**

Not possible



2) Use Gauss Theorem:

$$\sum q = 2\pi r * E$$



E = 300 kV/cm ➔ q ~ 10^{16} /cm^3

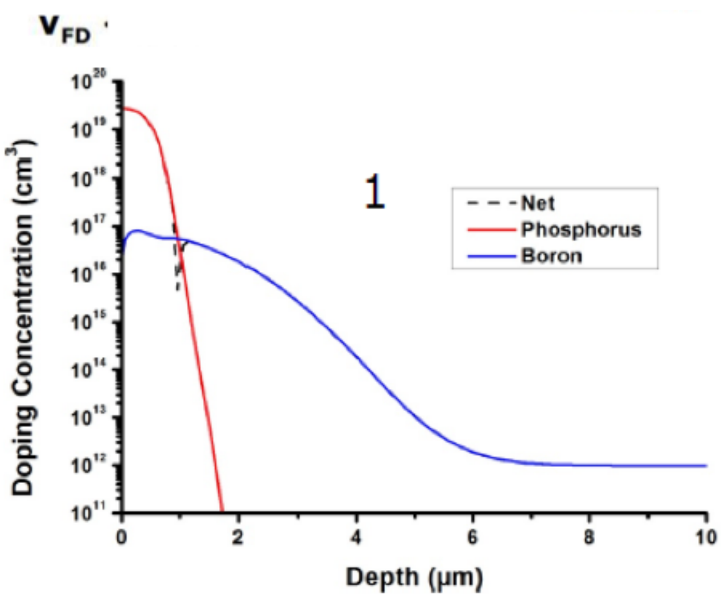
Low Gain Avalanche Detectors (LGADs)

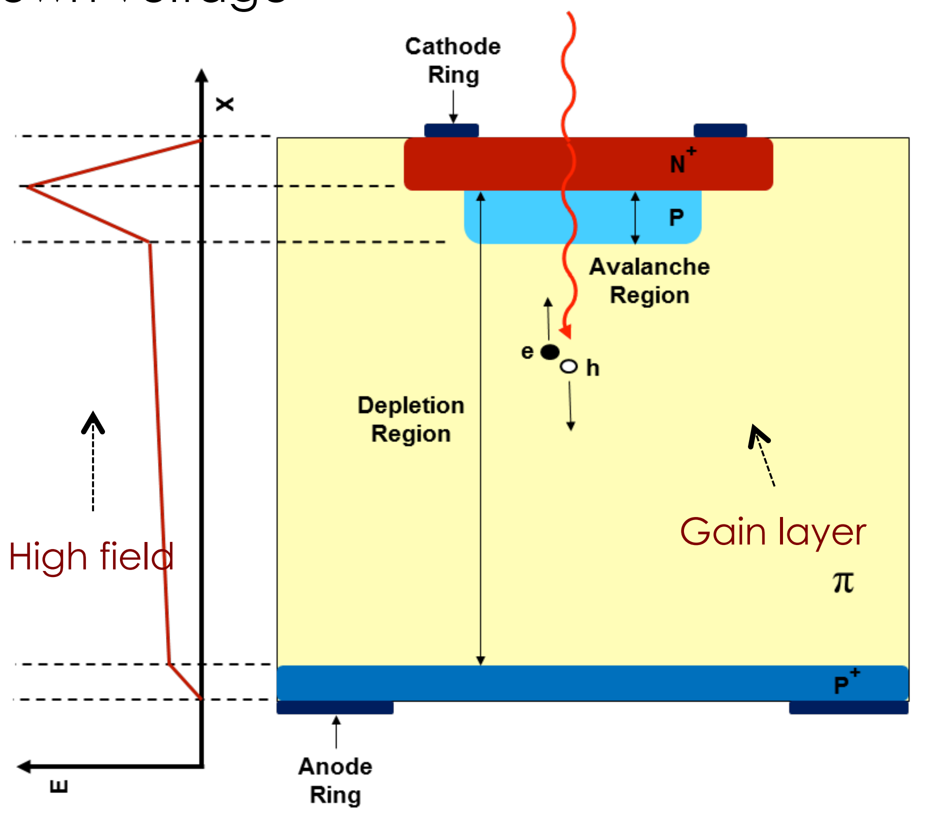
The LGAD sensors, as proposed and manufactured by CNM

(National Center for Micro-electronics, Barcelona):

High field obtained by adding an extra doping layer

E ~ 300 kV/cm, closed to breakdown voltage

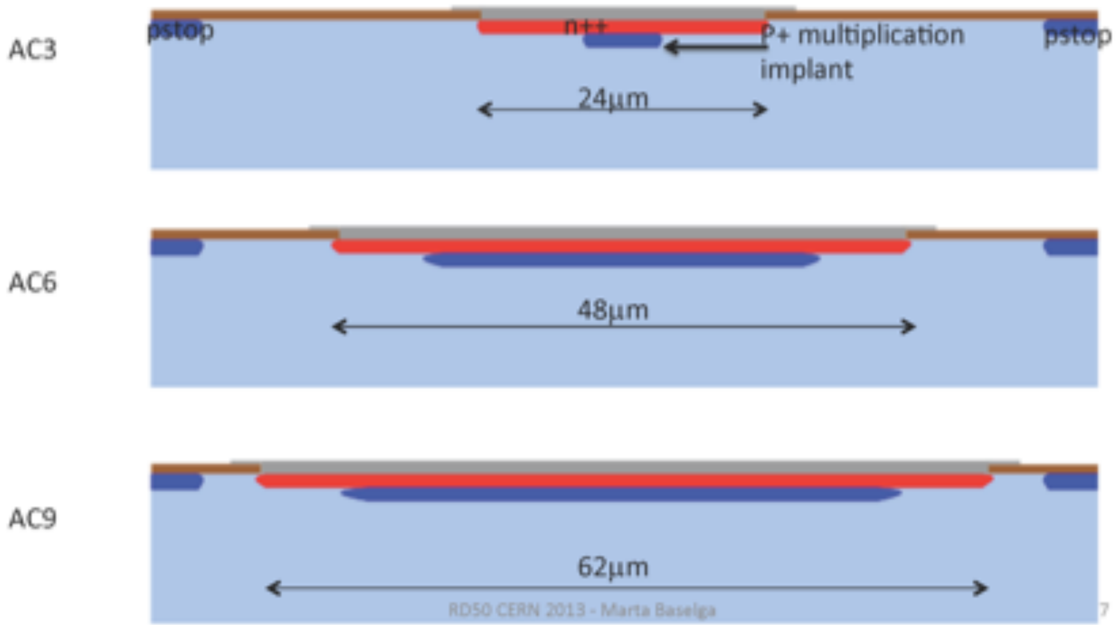


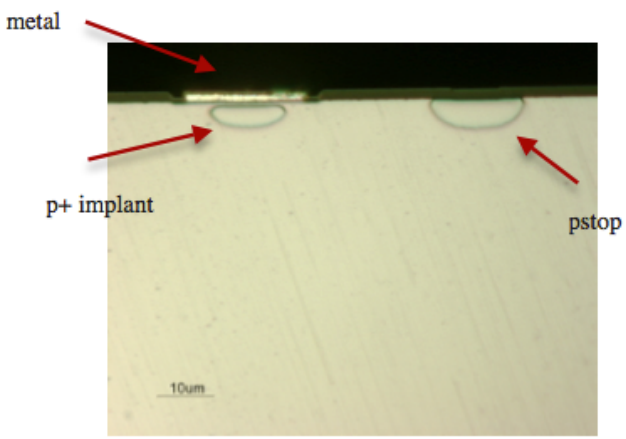


LGADs Pads, Pixels and Strips

The LGAD approach can be extended to any silicon structure, not just pads.

This is an example of LGAD strips





Sensor: Simulation

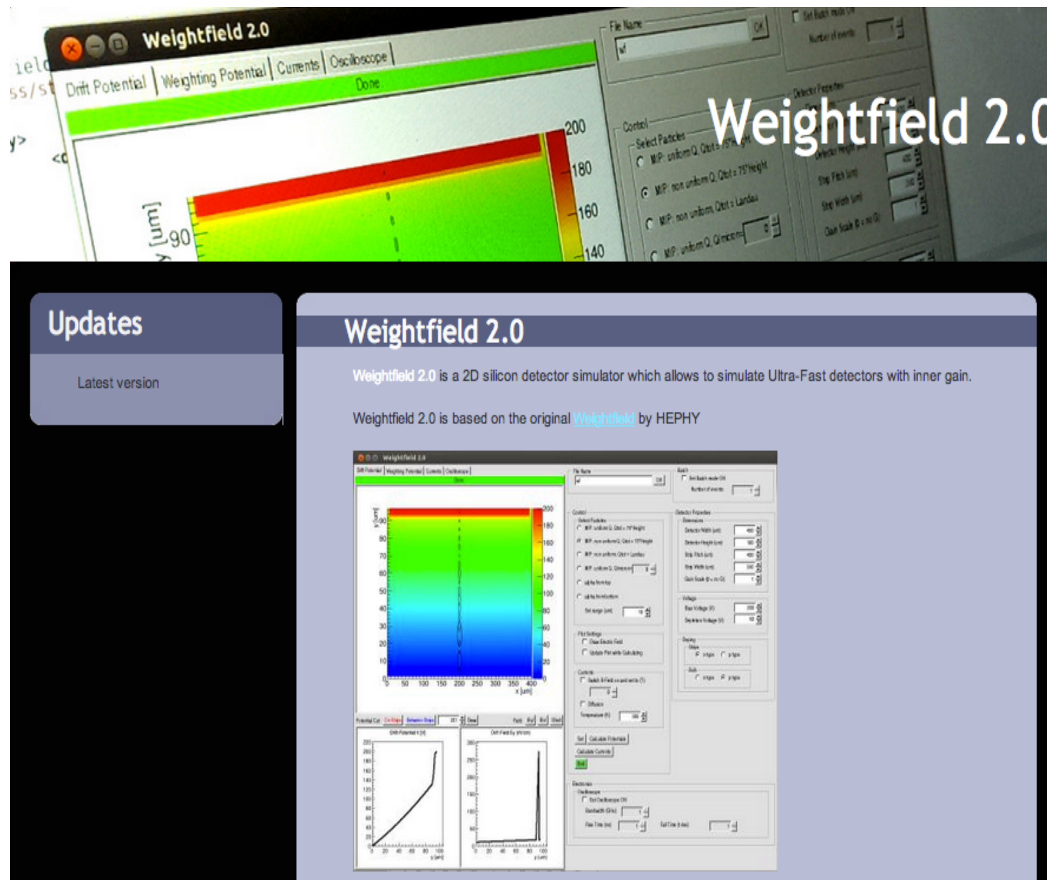
We developed a full sensor simulation to optimize the sensor design

WeightField2, F. Cenna, N. Cartiglia 9th Trento workshop, Genova 2014

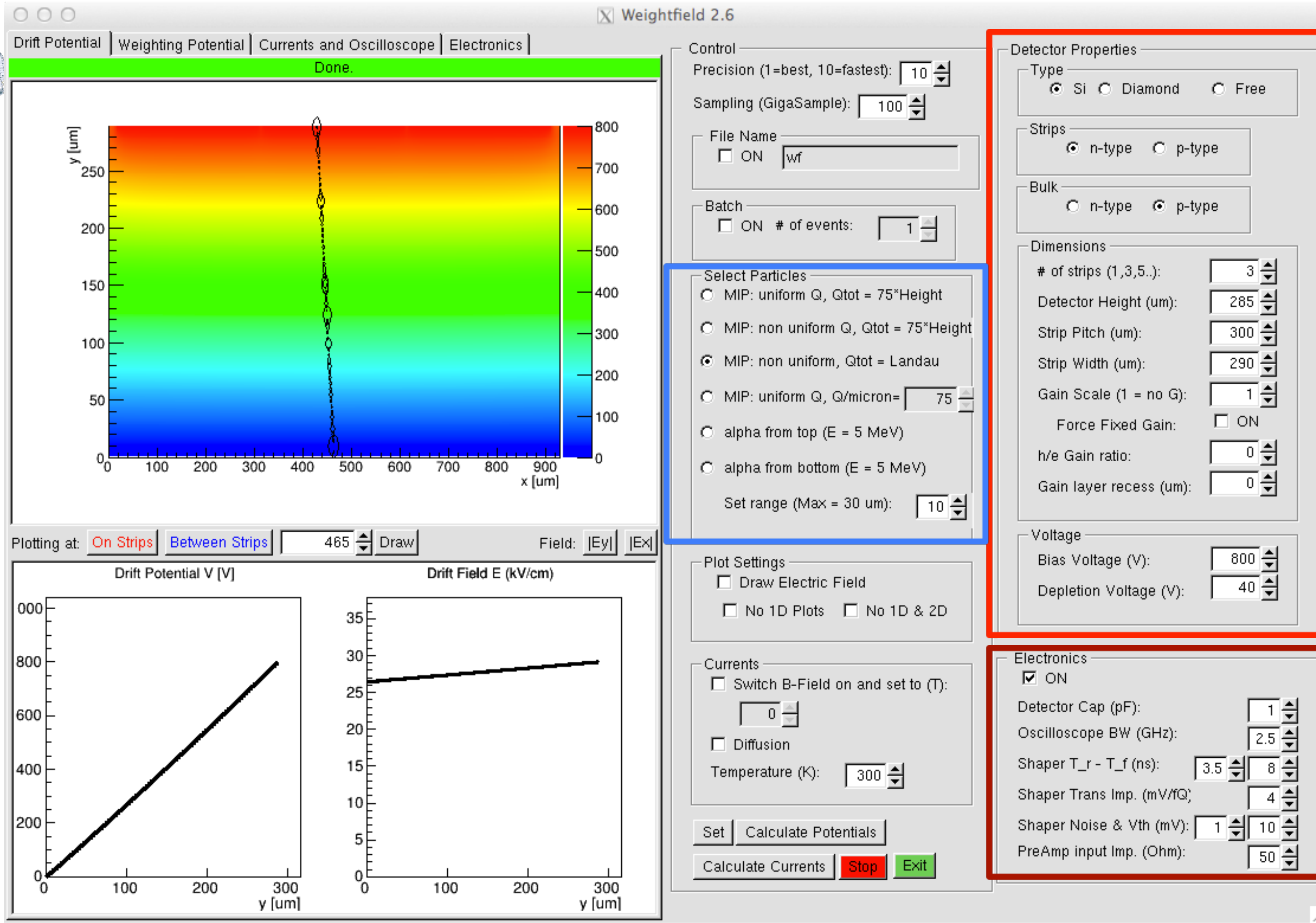
Available at http://personalpages.to.infn.it/~cartigli/weightfield2

It includes:

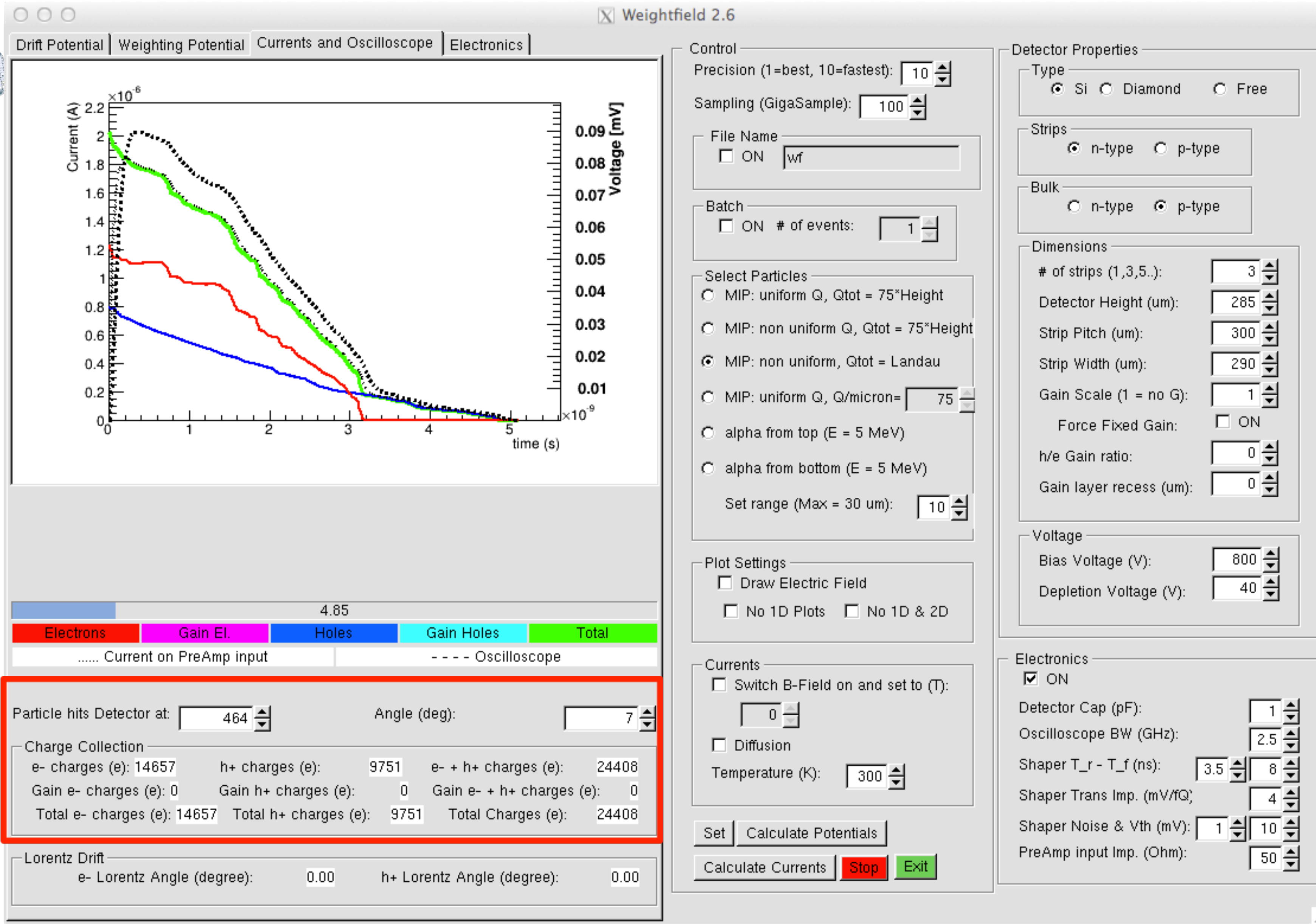
- Custom Geometry
- Calculation of drift field and weighting field
- Currents signal via Ramo's Theorem
- Gain
- Diffusion
- Temperature effect
- Non-uniformdeposition
- Electronics



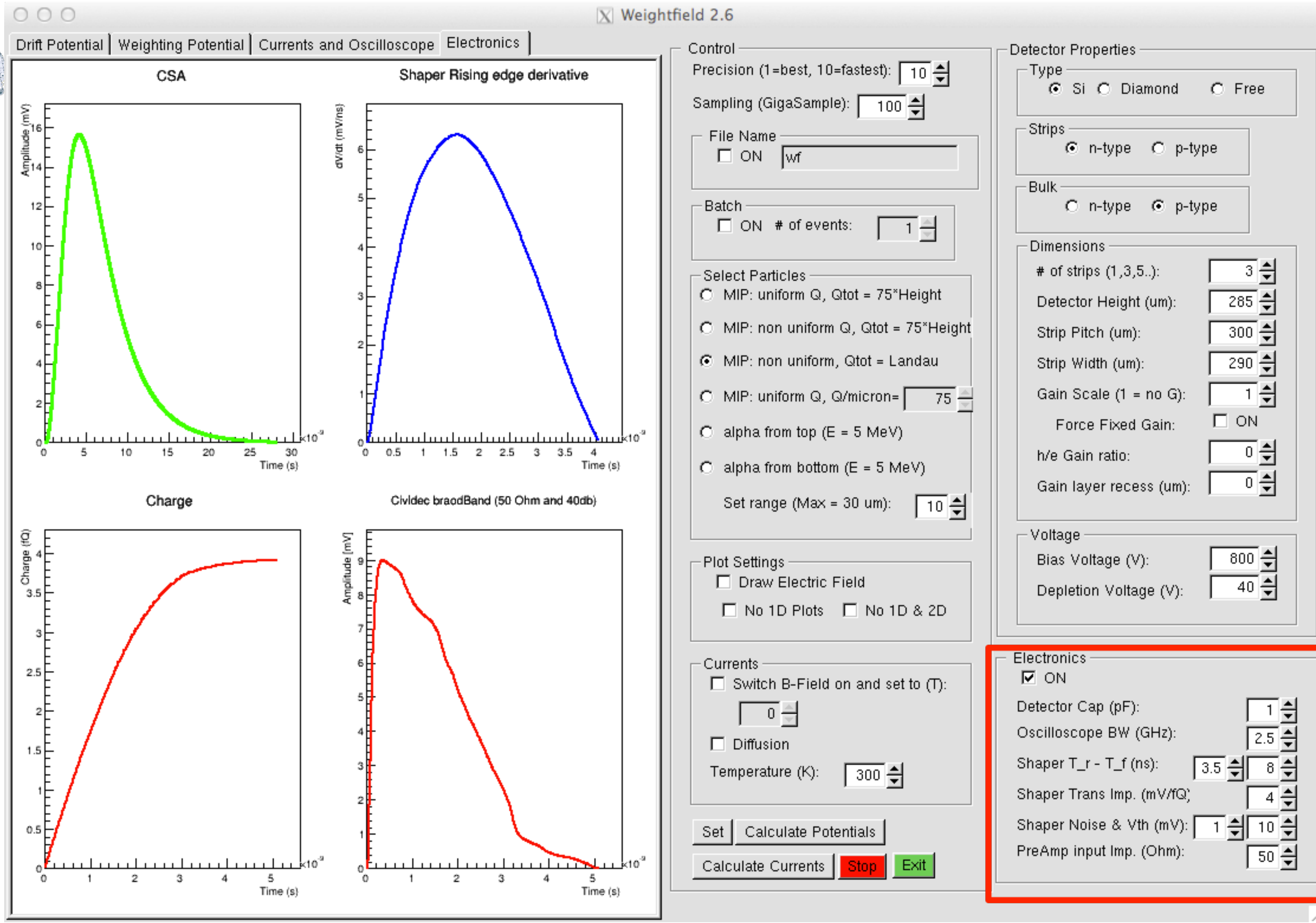
WeightField2: a program to simulate silicon detectors



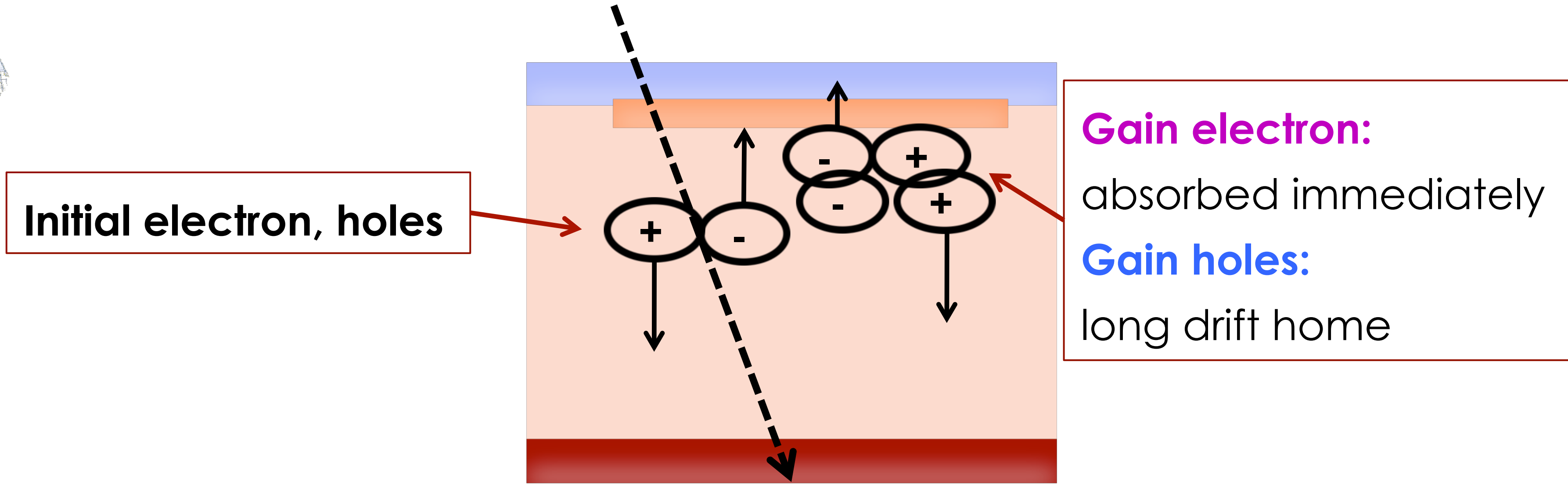
WeightField2: output currents

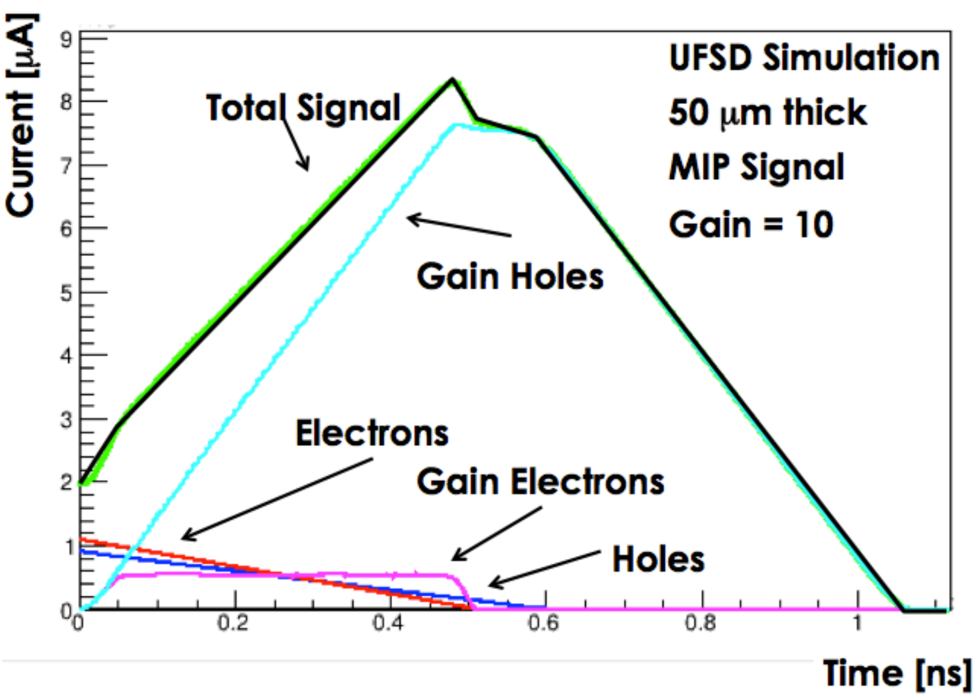


WeightField2: response of the read-out electronics



How gain shapes the signal





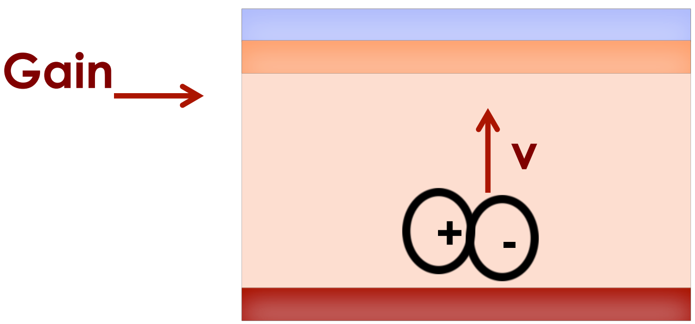
Electrons multiply and produce additional electrons and holes.

- **Gain electrons have almost no effect**
- **Gain holes dominate the signal**

➔ **No holes multiplications**

Interplay of gain and detector thickness

The rate of particles produced by the gain does not depend on *d* (assuming saturated velocity v_{sat})



Particles per micron

Gain

$$dN_{Gain} \propto 75(v_{sat}dt)G$$

➔ **Constant rate of production**

However the initial value of the **gain current depends on d** (via the weighing field)

$$di_{gain} \propto dN_{Gain} q v_{sat} \left(\frac{k}{d}\right)$$

➔ **Gain current ~ 1/d**

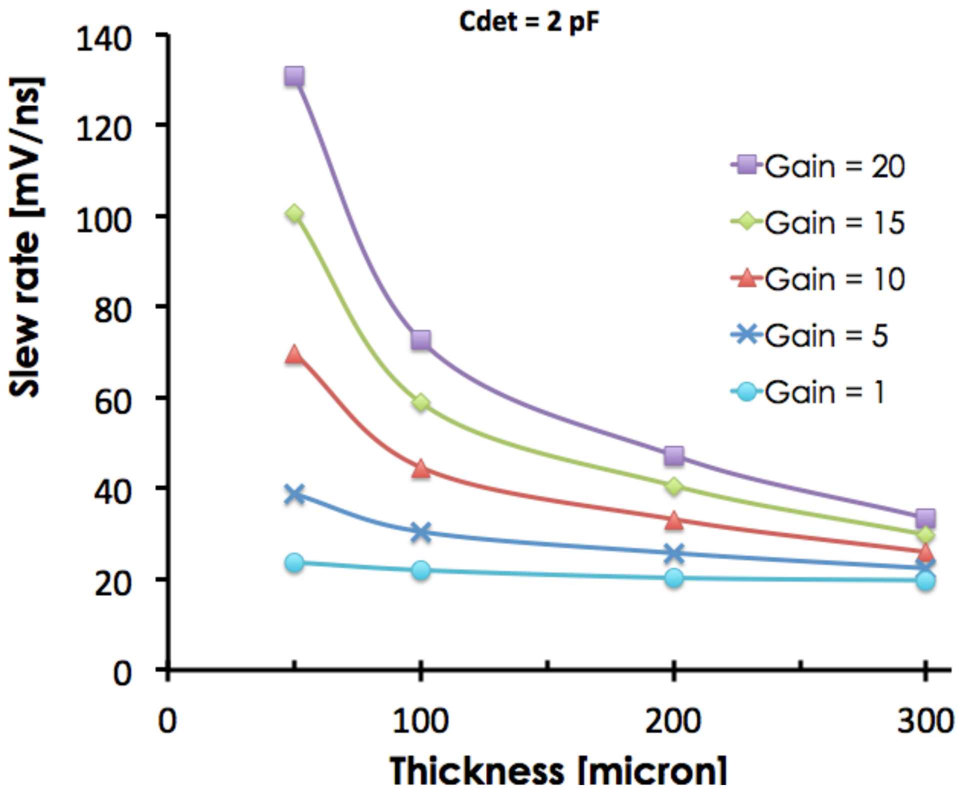
A given value of gain has much more effect on thin detectors

Gain current vs Initial current

$$\frac{di_{gain}}{i} \propto \frac{dN_{Gain} q v_{sat} \frac{k}{d}}{k q v_{sat}} = \frac{75(v_{sat} dt) G q v_{sat} \frac{k}{d}}{k q v_{sat}} \propto \frac{G}{d} dt$$

!!!

➔ Go thin!!



(Real life is a bit more complicated, but the conclusions are the same)

Full simulation

(assuming 2 pF detector capacitance)

300 micron:
~ 2-3 improvement with gain = 20

Significant improvements in time resolution require thin detectors

Ultra Fast Silicon Detectors

UFSD are LGAD detectors optimized to achieve the best possible time resolution

Specifically:

1. Thin to maximize the slew rate (dV/dt)
2. Parallel plate – like geometries (pixels..) for most uniform weighting field
3. High electric field to maximize the drift velocity
4. Highest possible resistivity to have uniform E field
5. Small size to keep the capacitance low
6. Small volumes to keep the leakage current low (shot noise)

First Measurements and future plans

LGAD laboratory measurements

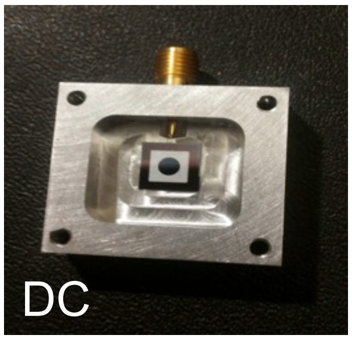
- Doping concentration
- Gain
- Time resolution measured with laser signals

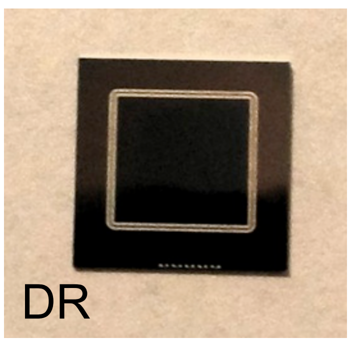
LGAD Testbeam measurements

- Landau shape at different gains
- Time resolution measured with MIPs

LGAD Sensors in Torino

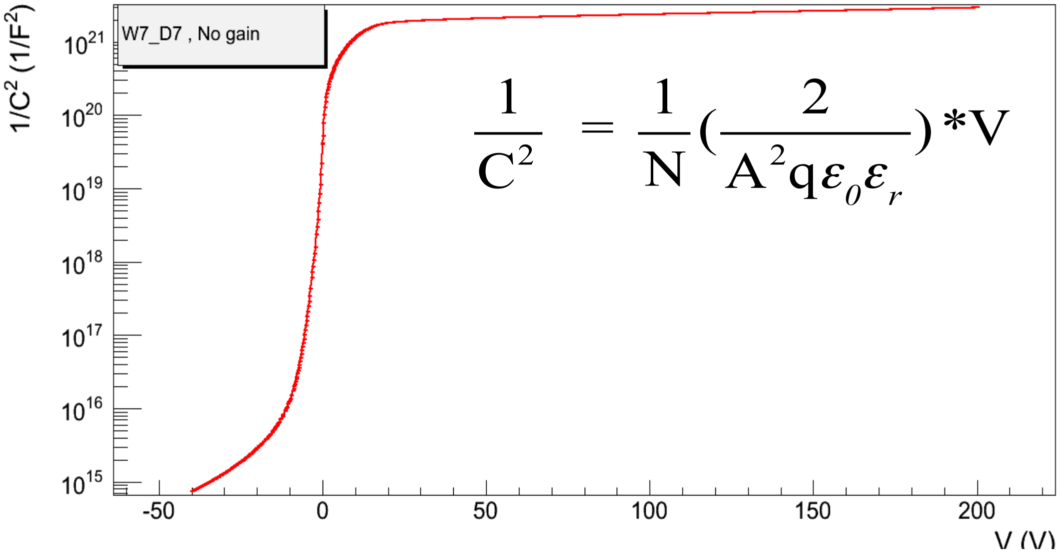
Thickness:
300 μm





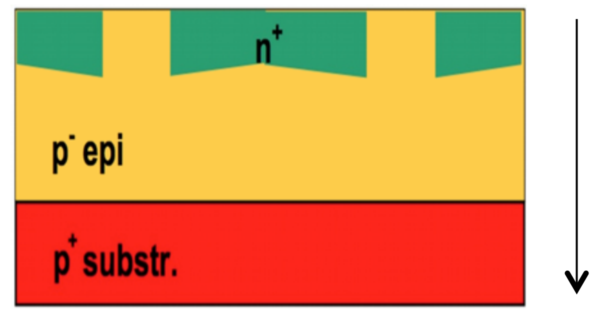
Run	Sensor	P-Layer Implant (E=100 KeV)	Gain	V_{break}	Metal Layer
6474	W8_B4	?	~ 10	> 500 V	DR
6474	W8_C6	?	~ 10	> 500 V	DC
6474	W9_B6	No implant	No Gain	> 500 V	DR
7062	W1_F3	1.6×10^{13} cm^{-2}	~ 1-2	> 500 V	DR
7062	W3_H5	2.0×10^{13} cm^{-2}	~ 10	> 500 V	DR
7062	W7_D7	No implant	No Gain	> 500 V	DR

Doping profile from CV measurement - I

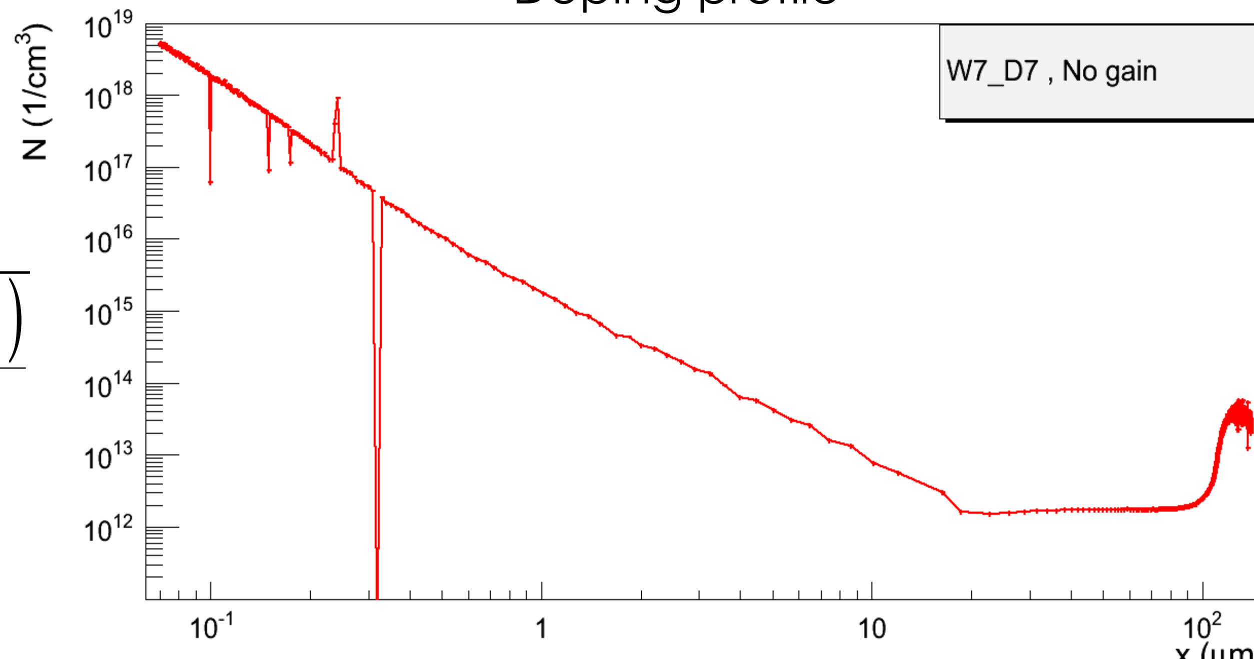


$$\frac{1}{C^2} = \frac{1}{N}\left(\frac{2}{A^2 q \varepsilon_0 \varepsilon_r}\right) * V$$

No-gain sensor



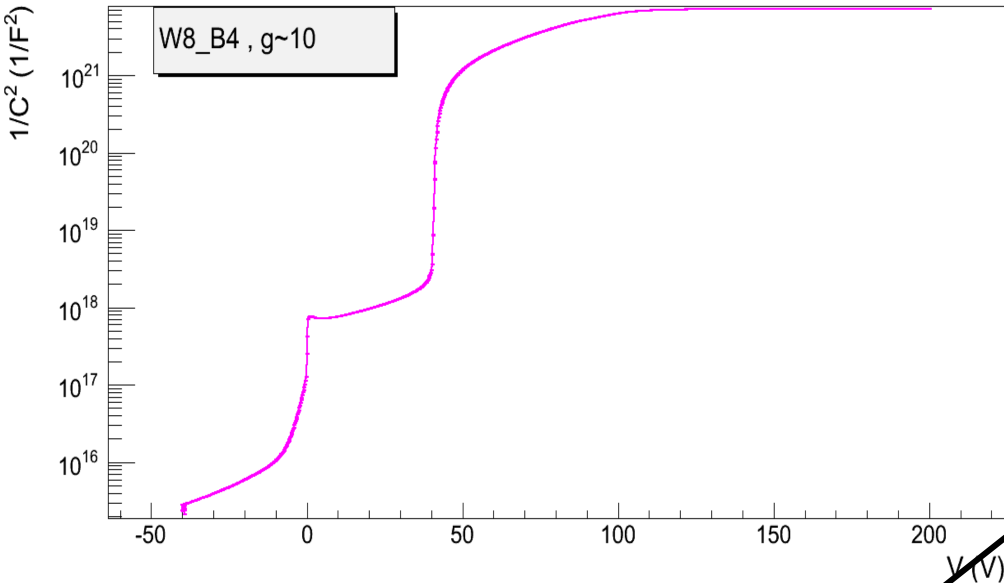
Doping profile

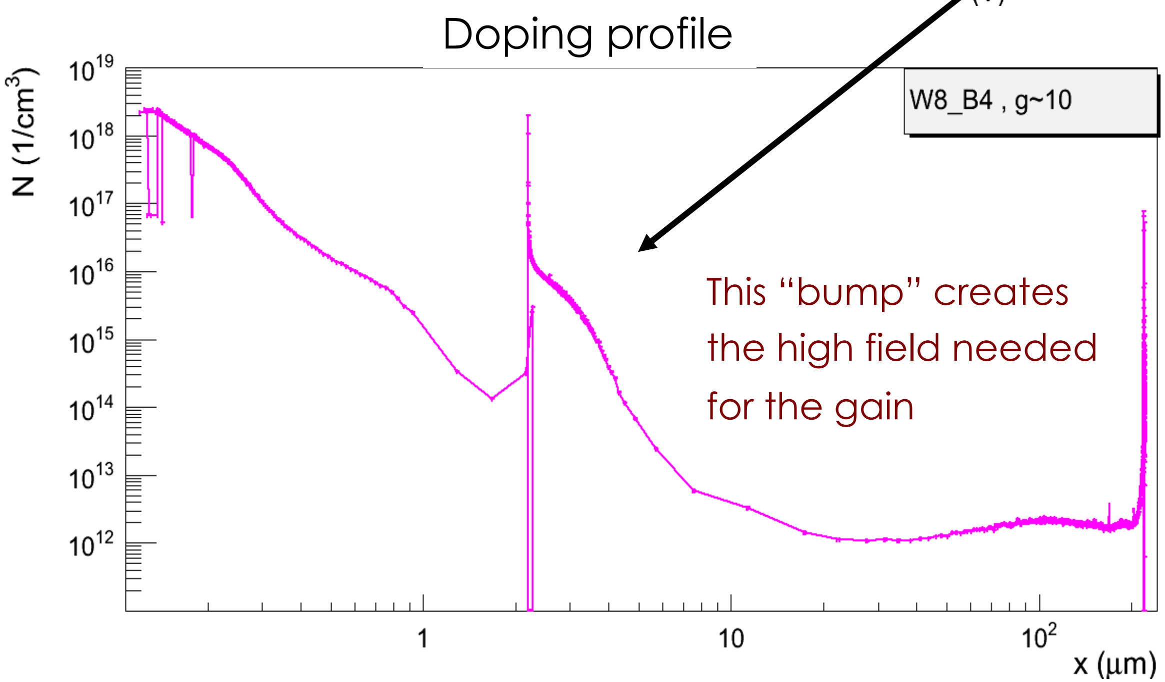


$$N = \frac{2}{q \varepsilon_0 \varepsilon_r A^2 \frac{d\left(1/C^2\right)}{dV}}$$

Doping

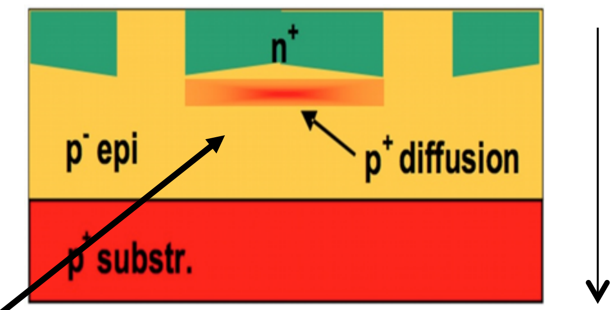
Doping profile from CV measurement - II

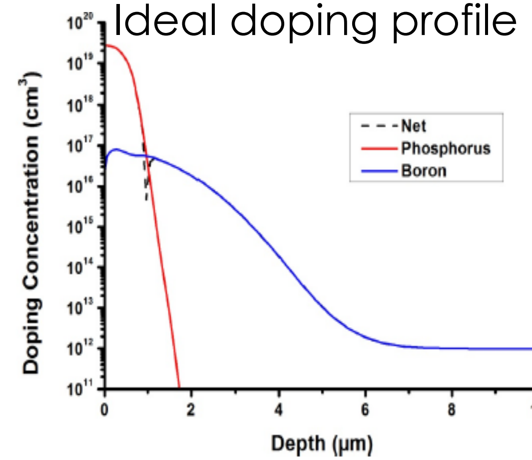




This "bump" creates the high field needed for the gain

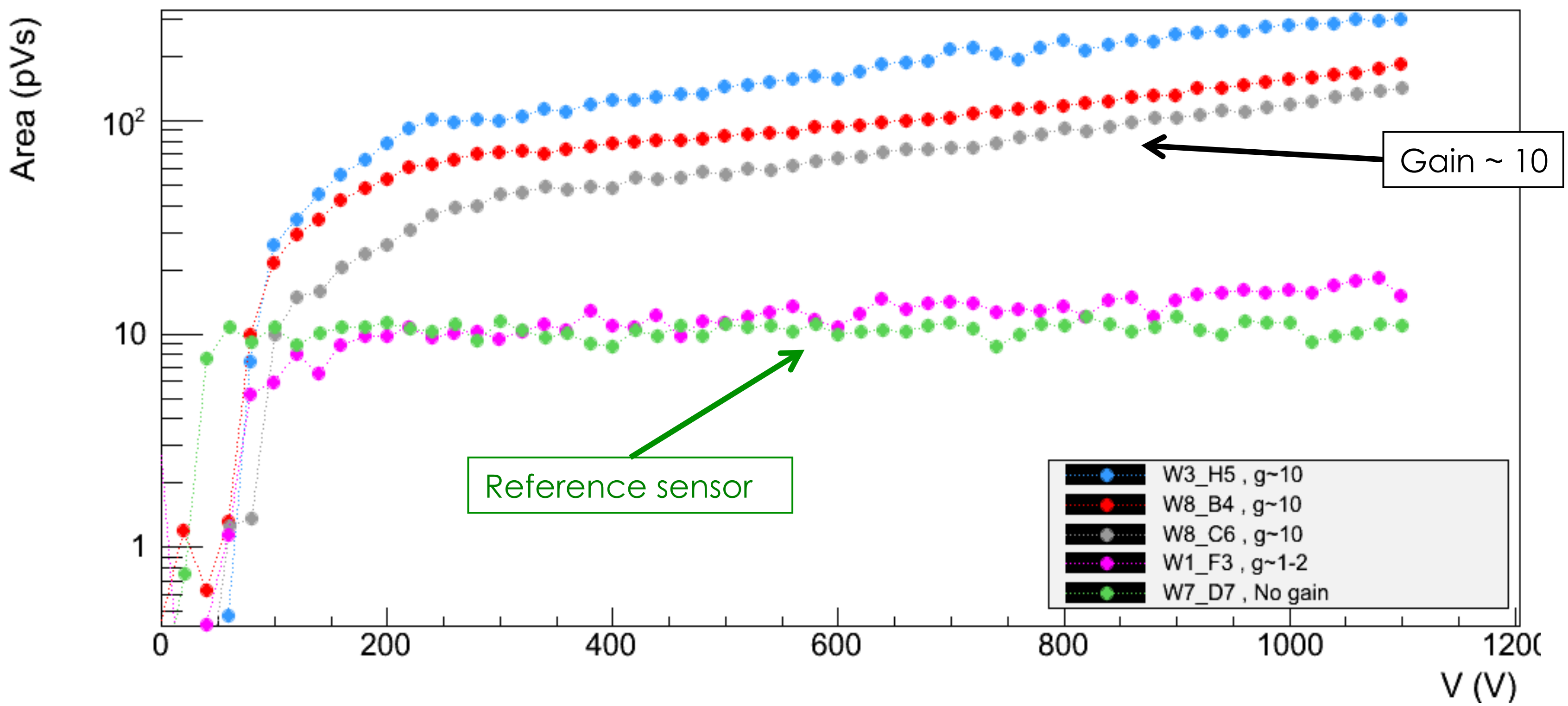
Gain sensor





Signal amplitude

Using laser signals we are able to measure the different responses of LGAD and traditional sensors

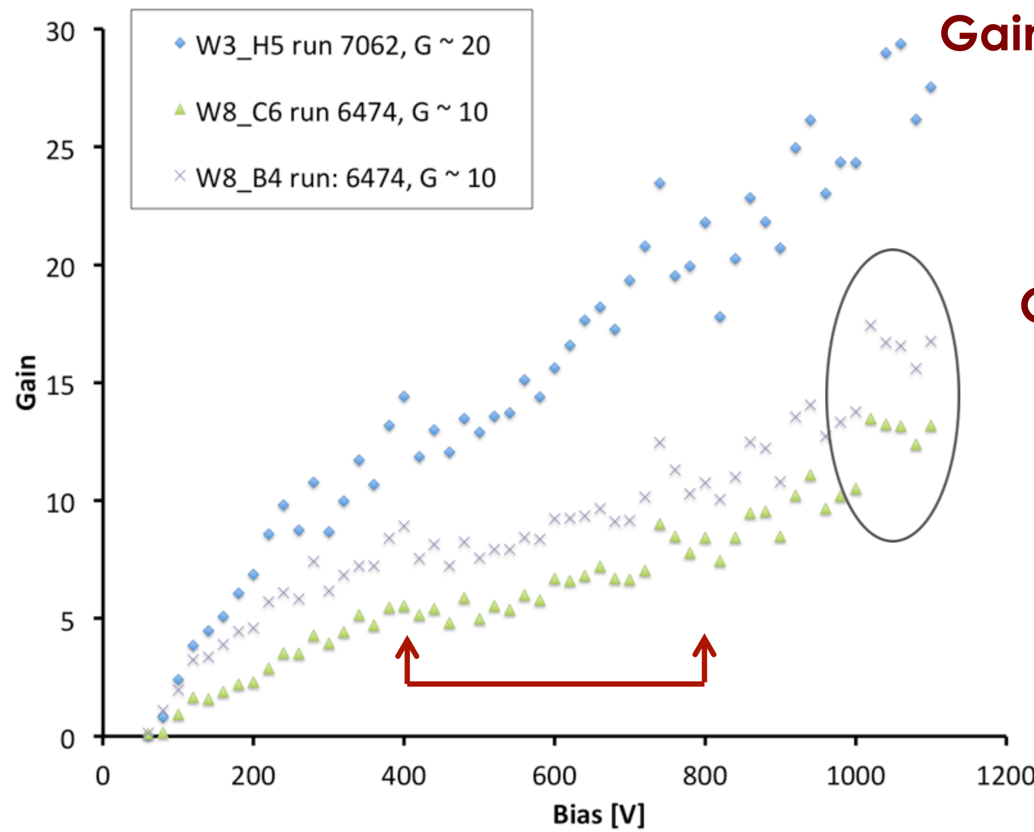


Gain

The gain is estimated as the ratio of the output signals of LGAD detectors to that of traditional one

The gain increases linearly with Vbias (not exponentially!)

$$\frac{\text{Gain @ 800V}}{\text{Gain @ 400V}} \sim 2$$



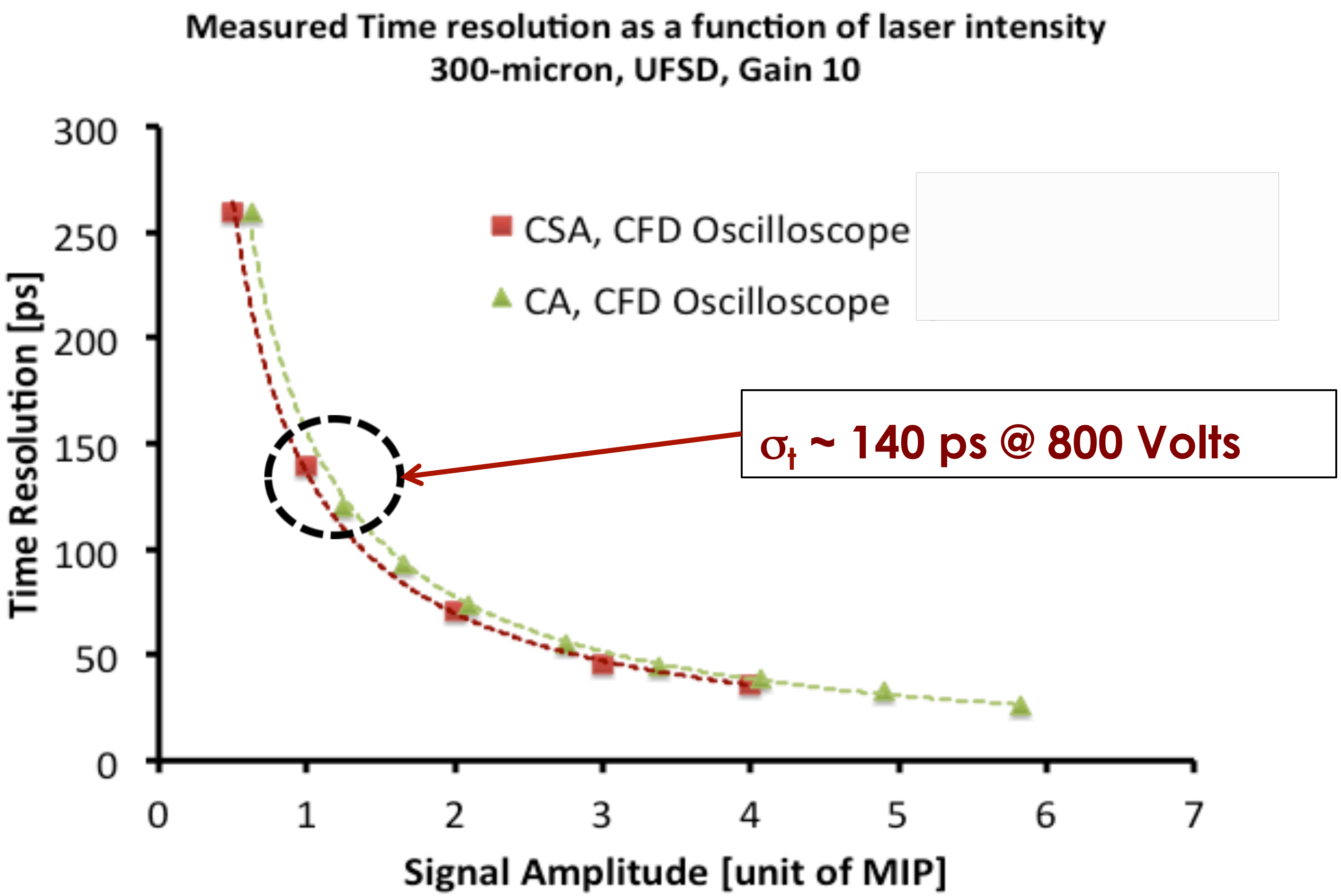
Gain ~ 20

Gain ~ 10

Laser Measurements on CNM LGAD

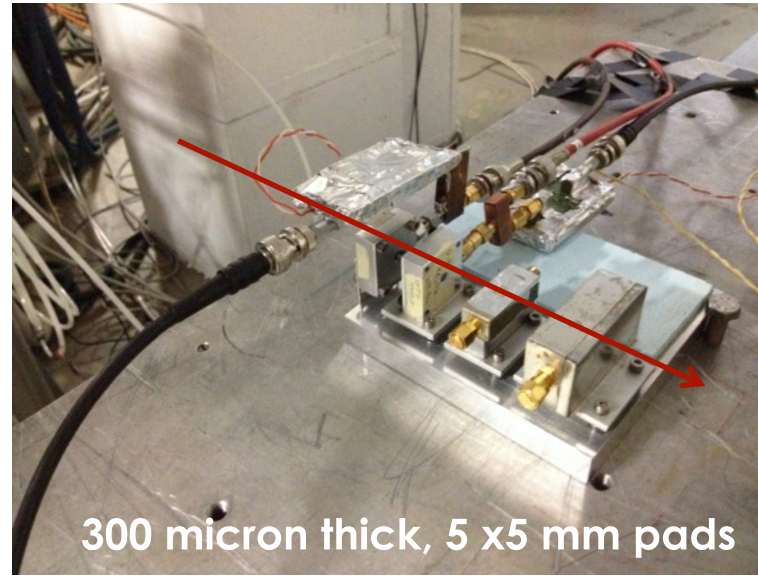
We use a 1064 nm picosecond laser to emulate the signal of a MIP particle (without Landau Fluctuations)

The signal output is read out by either a Charge sensitive amplifier or a Current Amplifier (Cividec)

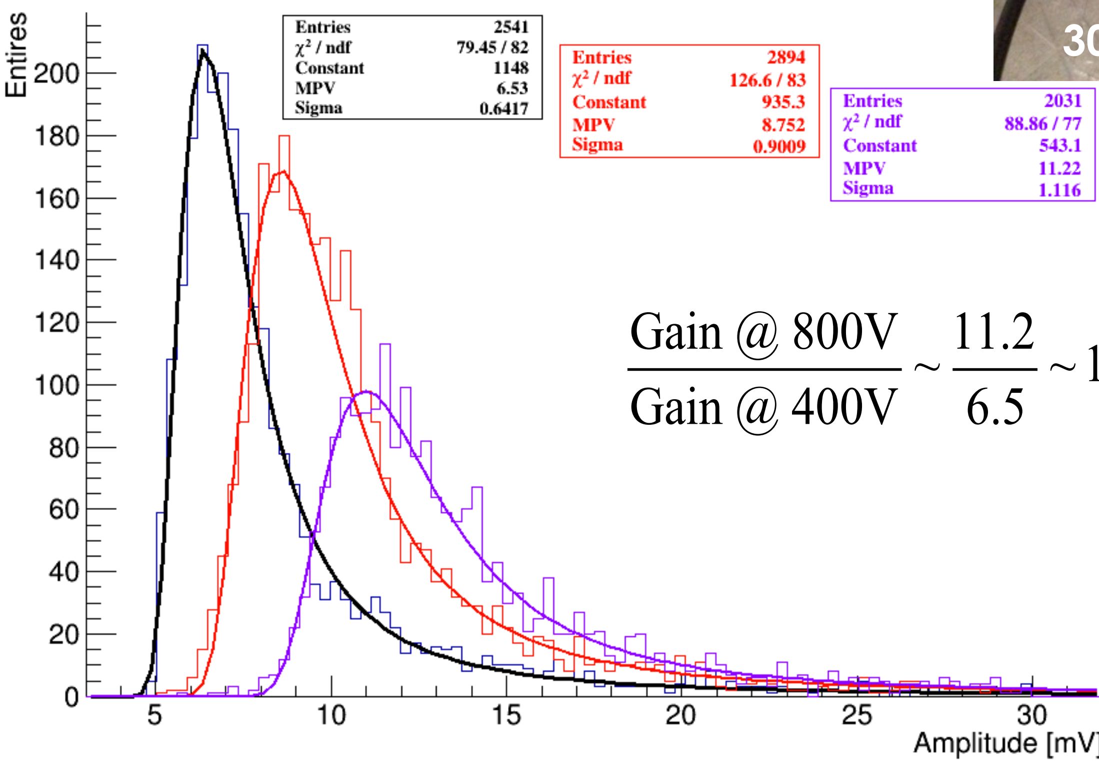


Testbeam Measurements on CNM LGAD

In collaboration with Roma2, we went to Frascati for a testbeam using 500 MeV electrons



As measured in the lab, the gain ~ doubles going from 400 -> 800 Volt.



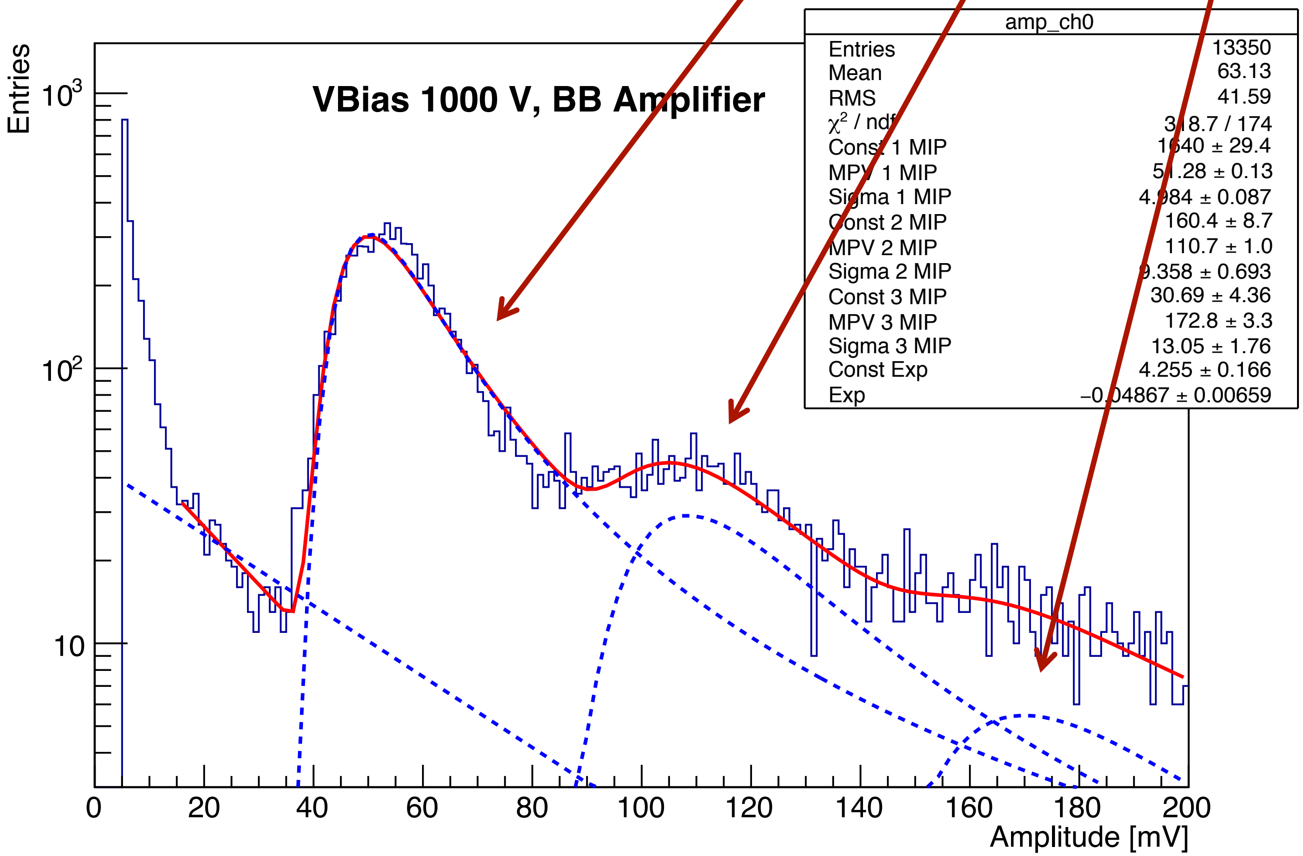
$$\frac{\text{Gain @ 800V}}{\text{Gain @ 400V}} \sim \frac{11.2}{6.5} \sim 1.7$$

The gain mechanism preserves the Landau amplitude distribution of the output signals

100 GeV pion Testbeam with CNM LGAD

Teasbeam data understood as the sum of 1MIP, 2 MIP or 3 MIP

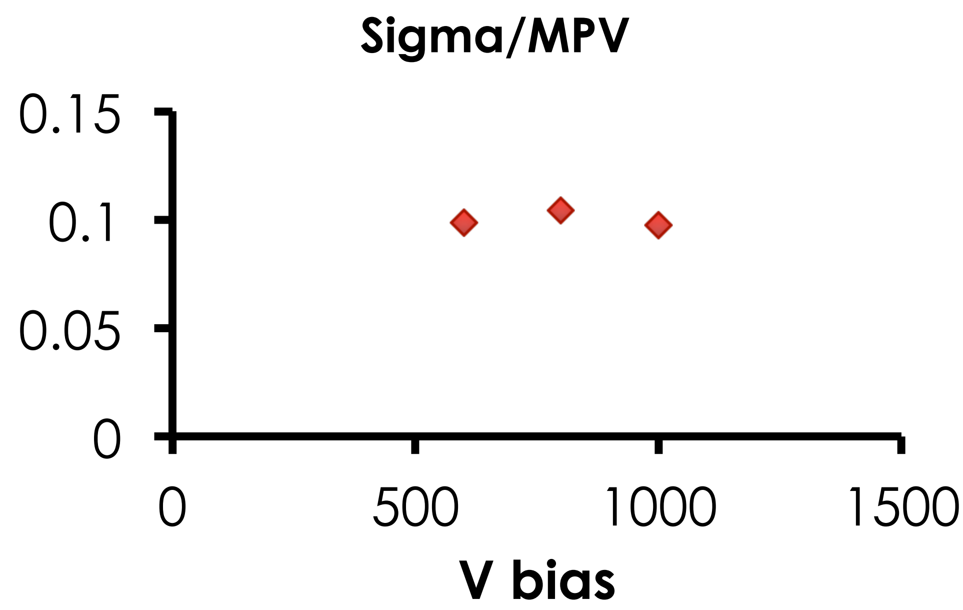
Very linear behavior of UFSD with increasing charge



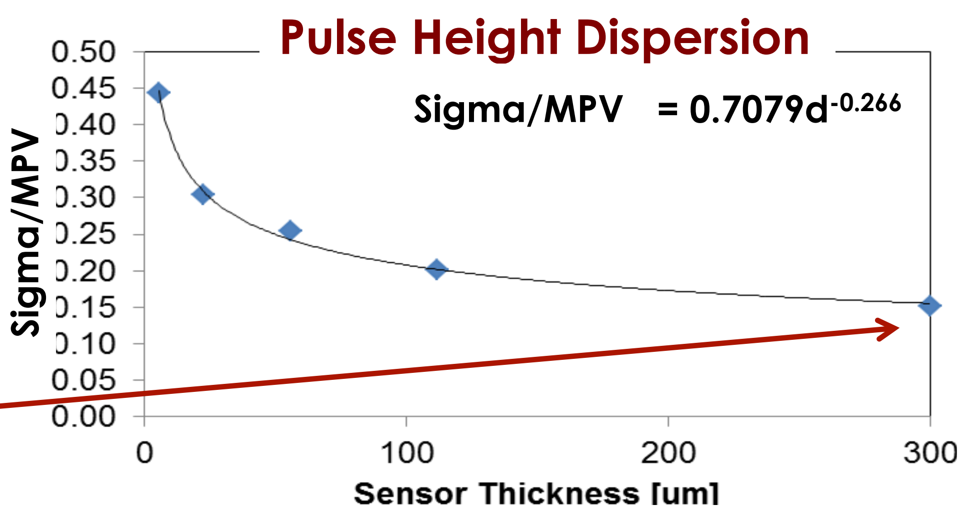
Properties of the Landau distributions

Nicolo Cartiglia, INFN, Torino - UFSD; DESY , 20 March 2015

The ratio sigma/MPV is constant as a function of multiplication indicating that the excess noise factor is not playing a role yet



According to our fits, the Landau have a smaller width than what is proposed by the parameterization of Meroli et al.

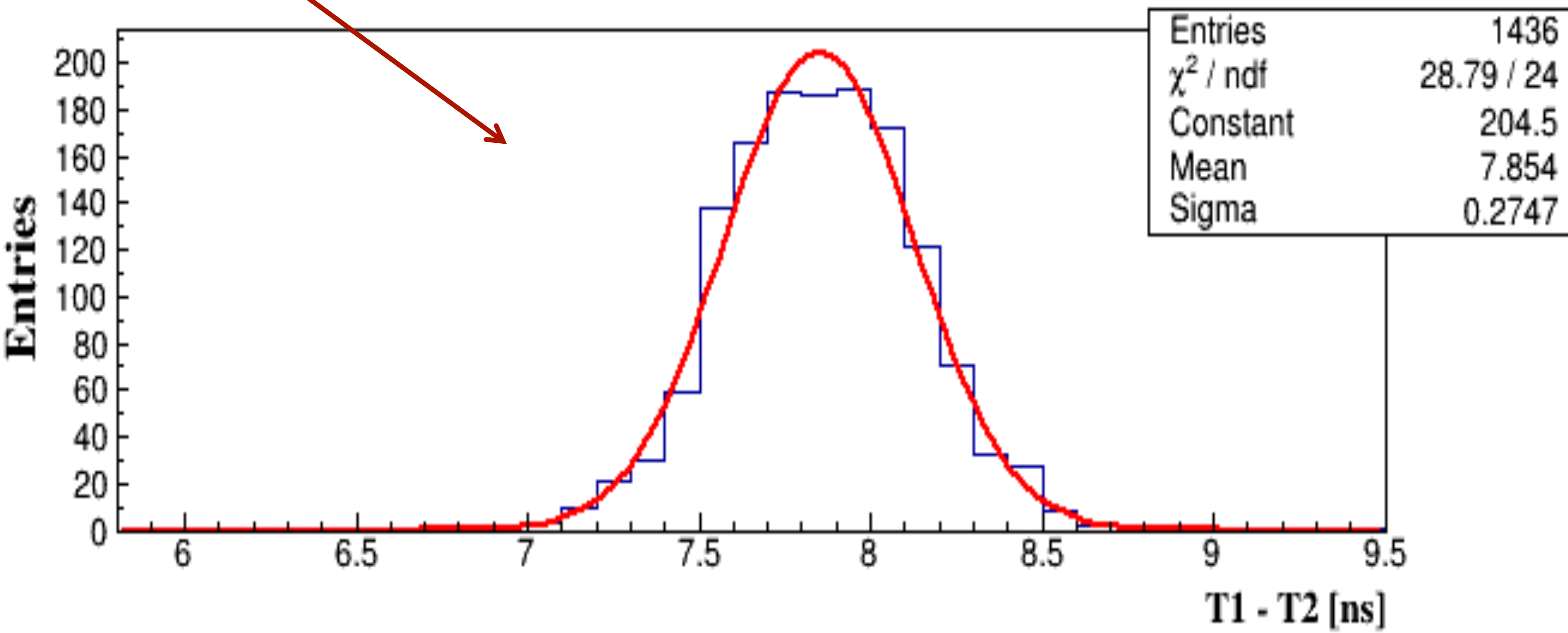


Testbeam Measurements on CNM LGAD

Time difference between two LGAD detectors crossed by a MIP

Tested different types of electronics (Rome2 SiGe, Cividec),
Not yet optimized for these detectors

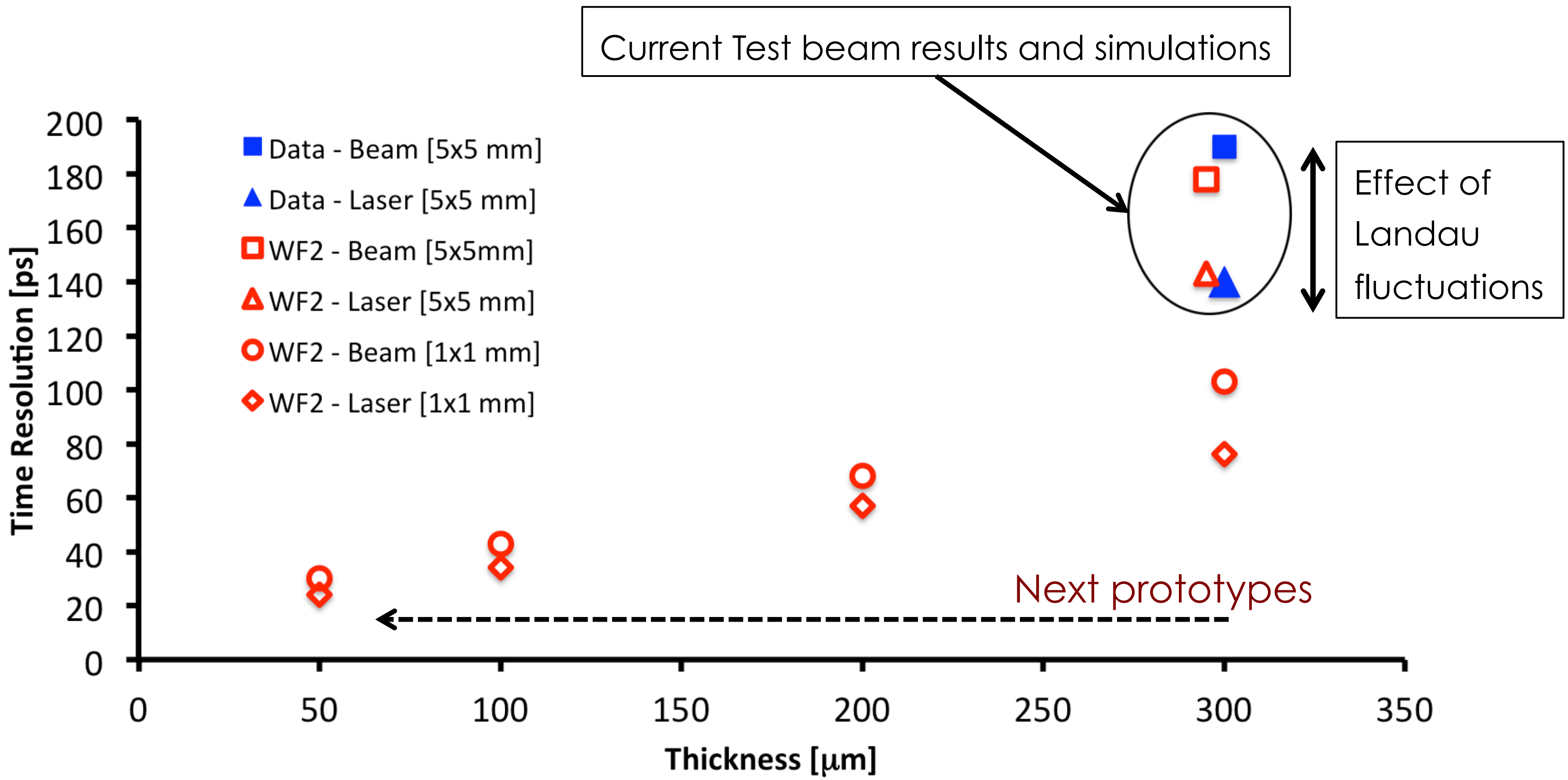
σ_t ~ 190 ps @ 800 Volts



Present results and future productions

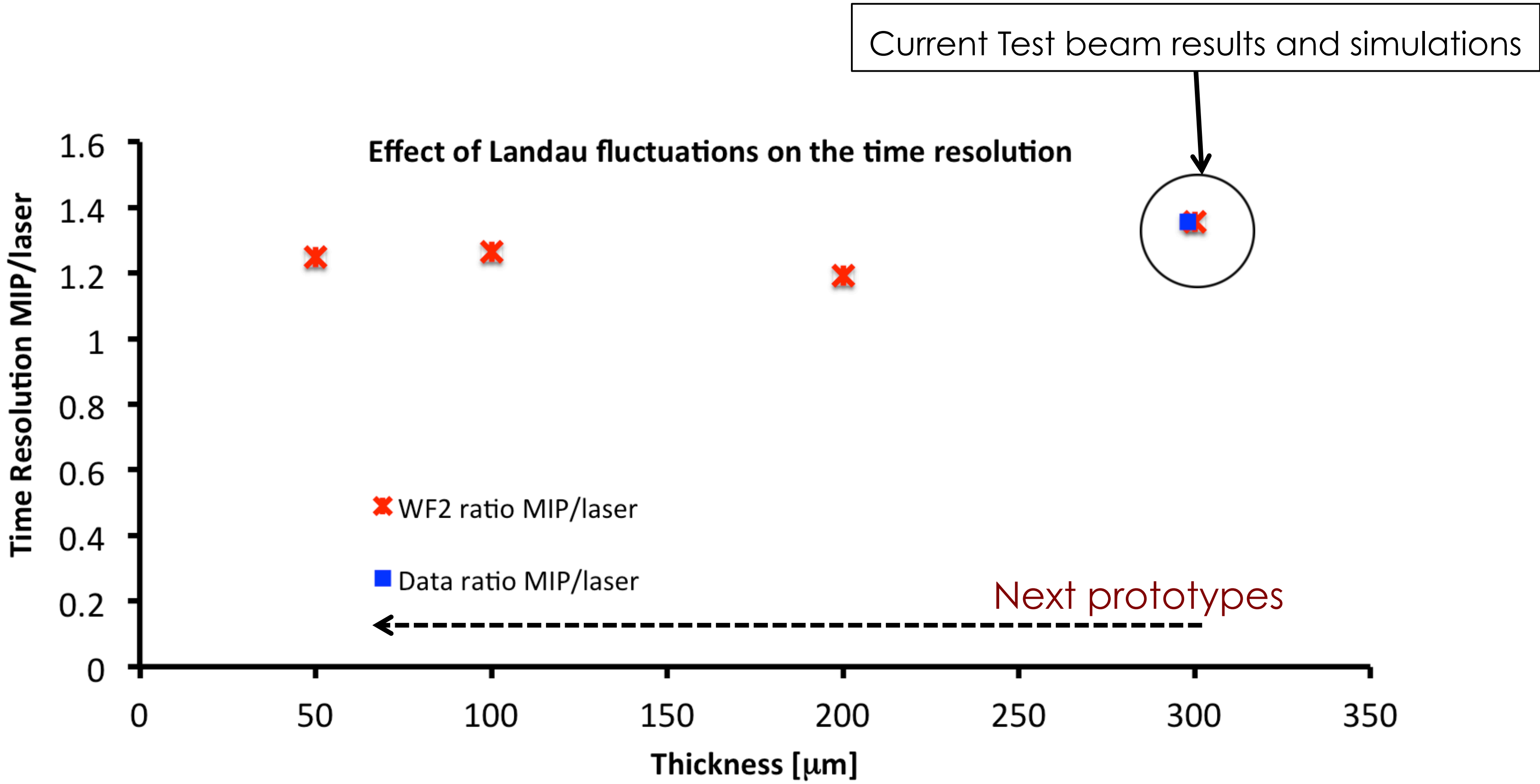
With WF2, we can reproduce very well the laser and testbeam results.

Assuming the same electronics, and 1 mm^2 LGAD pad with gain 10, we can predict the timing capabilities of the next sets of sensors.



Effect of Landau Fluctuations on the time resolution

The effect of Landau fluctuations in a MIP signal are degrading the time resolution by roughly 30 % with respect of a laser signal

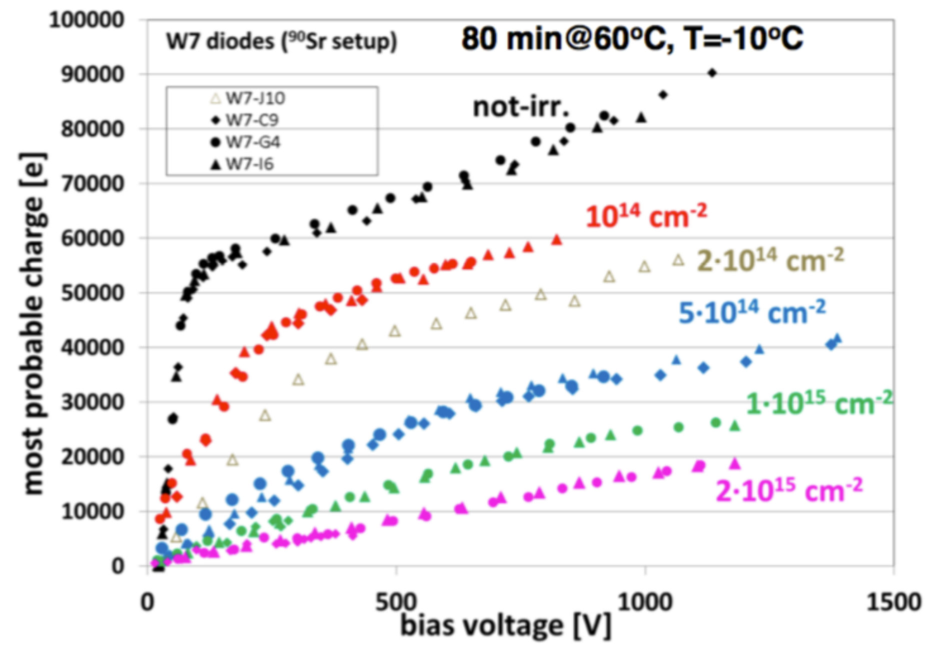


Nicolo Cartiglia, INFN, Torino - UFSD; DESY , 20 March 2015

Irradiation tests

The gain decreases with irradiations:
at 10^{14} n/cm^2 is 20% lower

➔ **Due to boron disappearance**



What-to-do next:

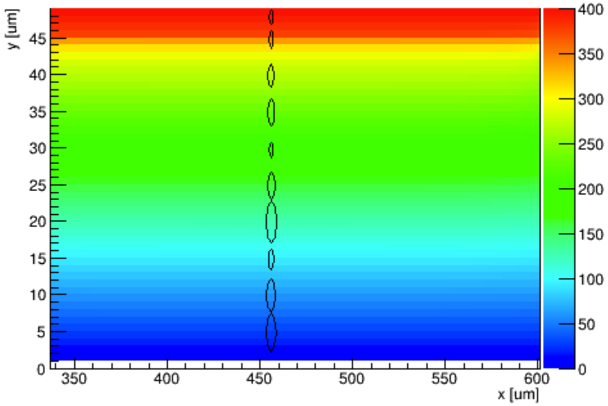
1) Planned new irradiation runs (neutrons, protons), new sensor geometries

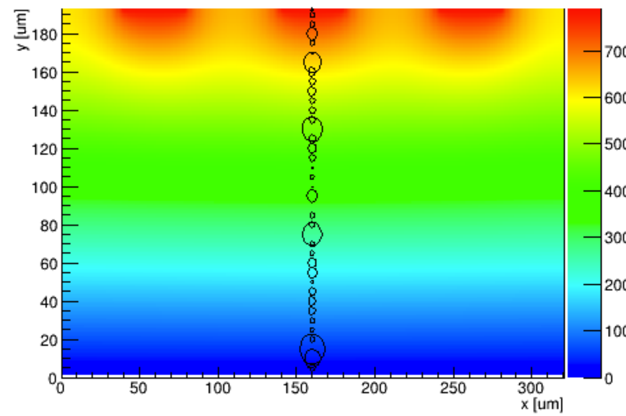
2) Use Gallium instead of Boron for gain layer (in production now)

3) Design the UFSD to have a gain higher than we need, ~ 30 at 500 V.
   - We use UFSD at gain 10-15, at 200 Volt
   - When radiation damage lowers the gain, we increase Vbias to compensate

Merging timing with position resolution

Electrode segmentation makes the E field very non uniform, and therefore ruins the timing properties of the sensor



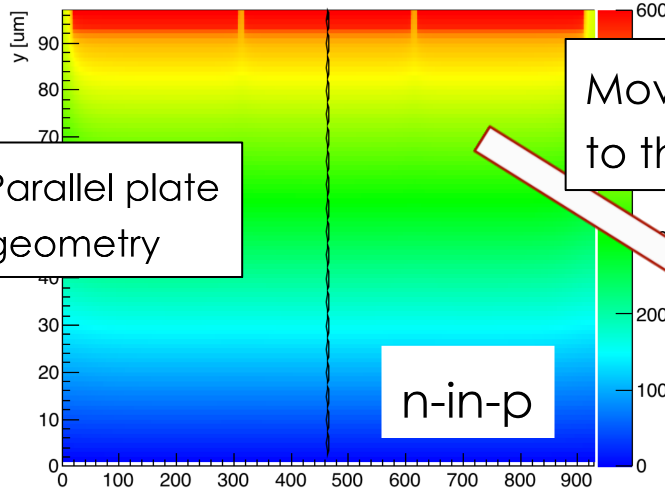


We need to find a geometry that has very uniform E field, while allowing electrode segmentation.

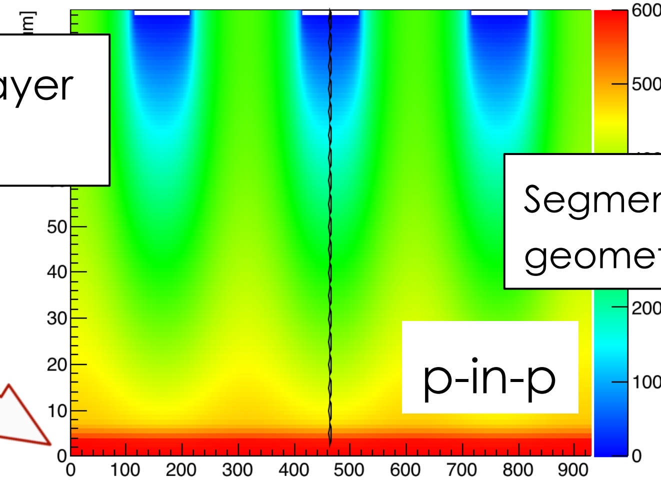
1) Segmentation: buried junction

Separate the multiplication side from the segmentation side

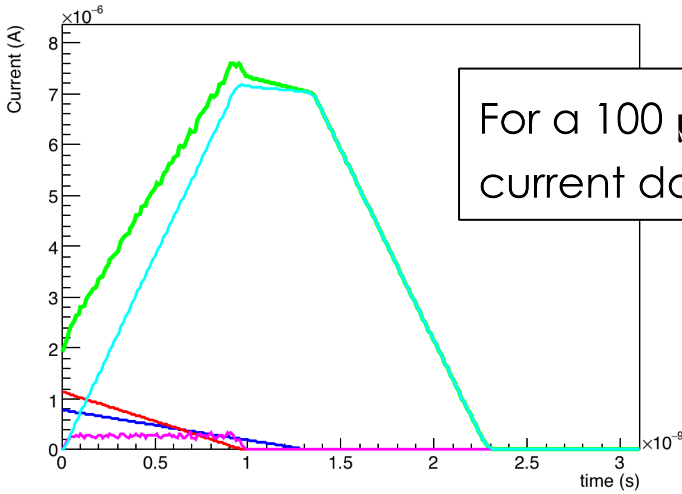
Parallel plate geometry



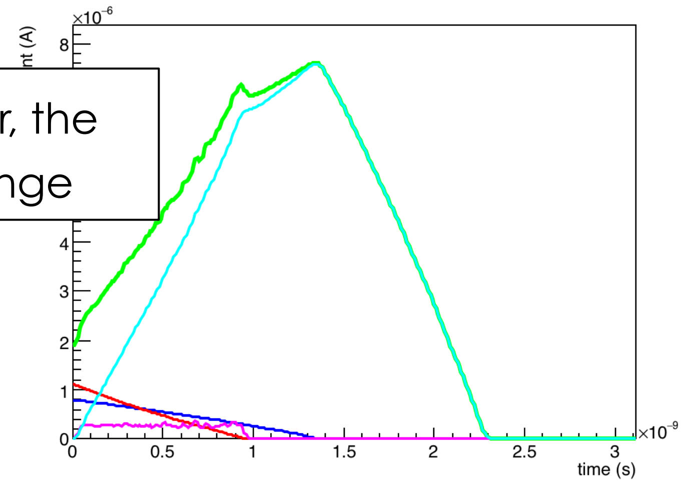
Move the gain layer to the deep side



Segmented geometry



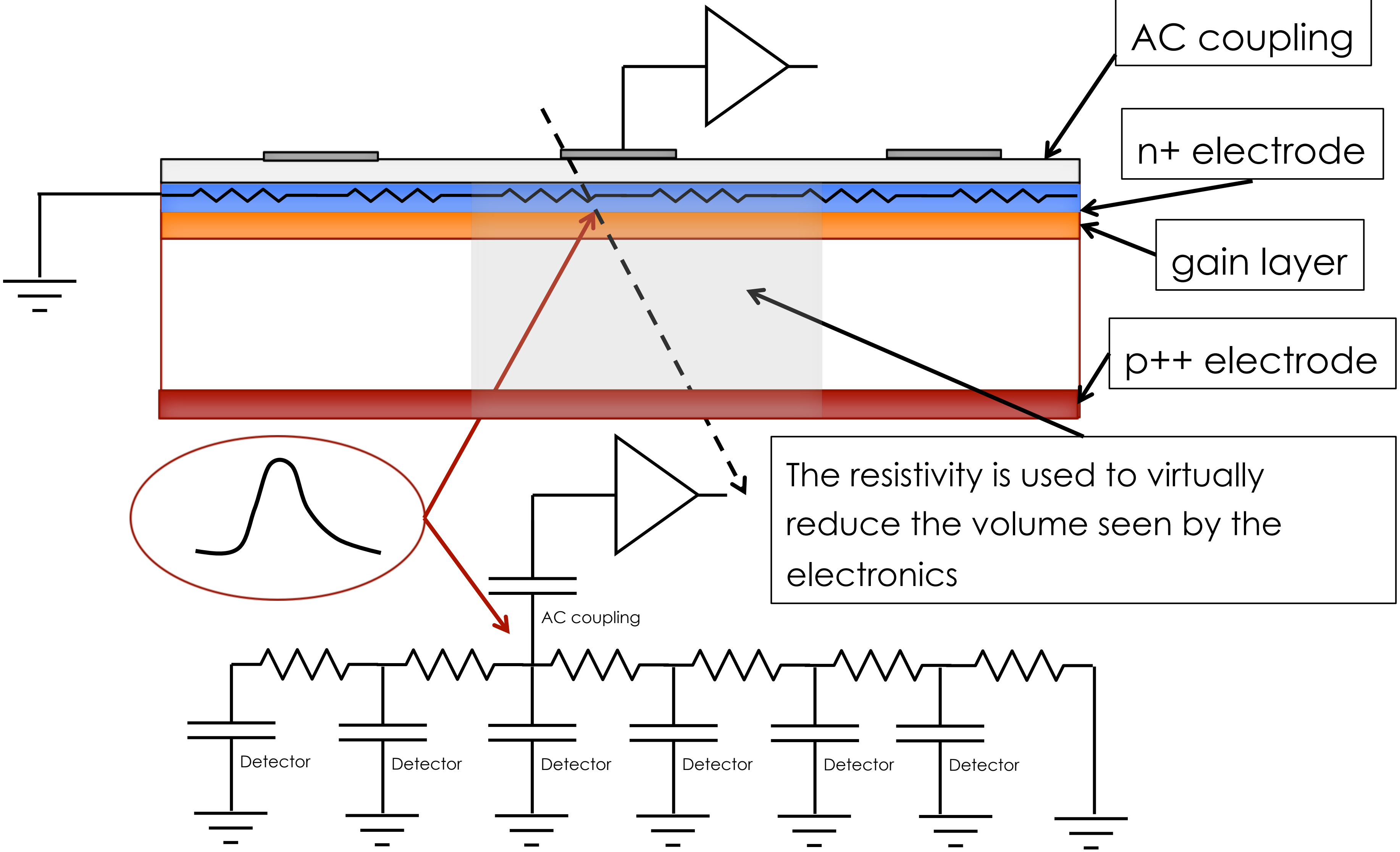
For a 100 μm detector, the current does not change



Moving the junction on the deep side allows having a very uniform multiplication, regardless of the electrode segmentation

2) Segmentation: AC coupling

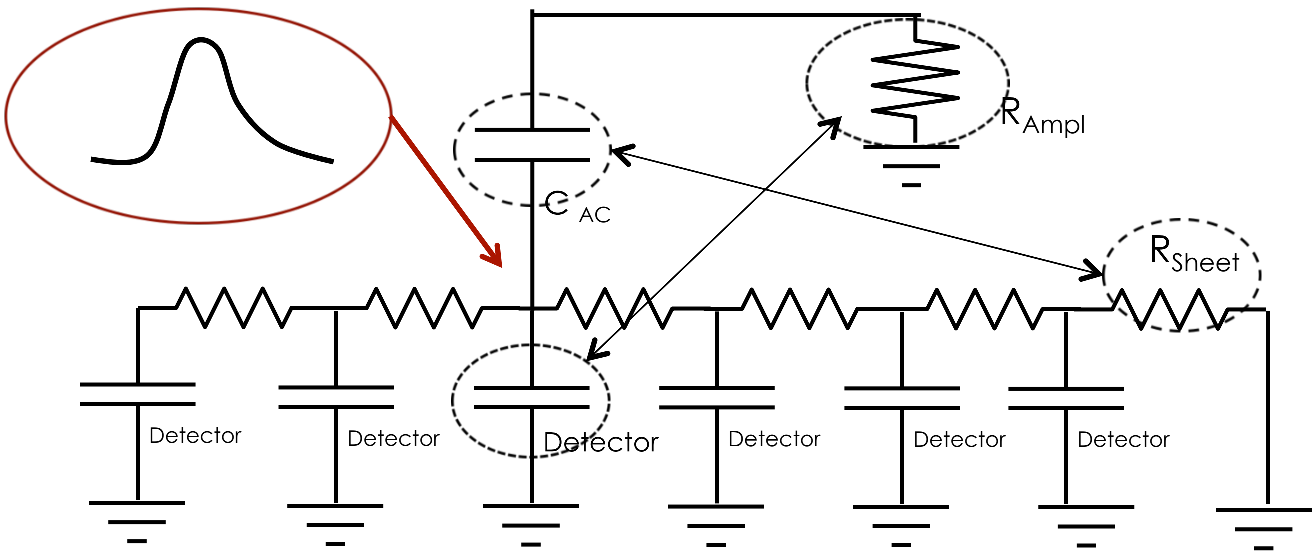
Standard n-in-p LGAD, with AC read-out



Details of Resistivity and AC coupling

Additional Rise time

$R_{Ampl} * C_{detector} \sim 100\ \Omega * 1pF \sim$ **100 ps**



Freezing time

$R_{Sheet} * C_{AC} \sim 1k\Omega * 100pF \sim 100$ ns

Only a small part of the detector is involved

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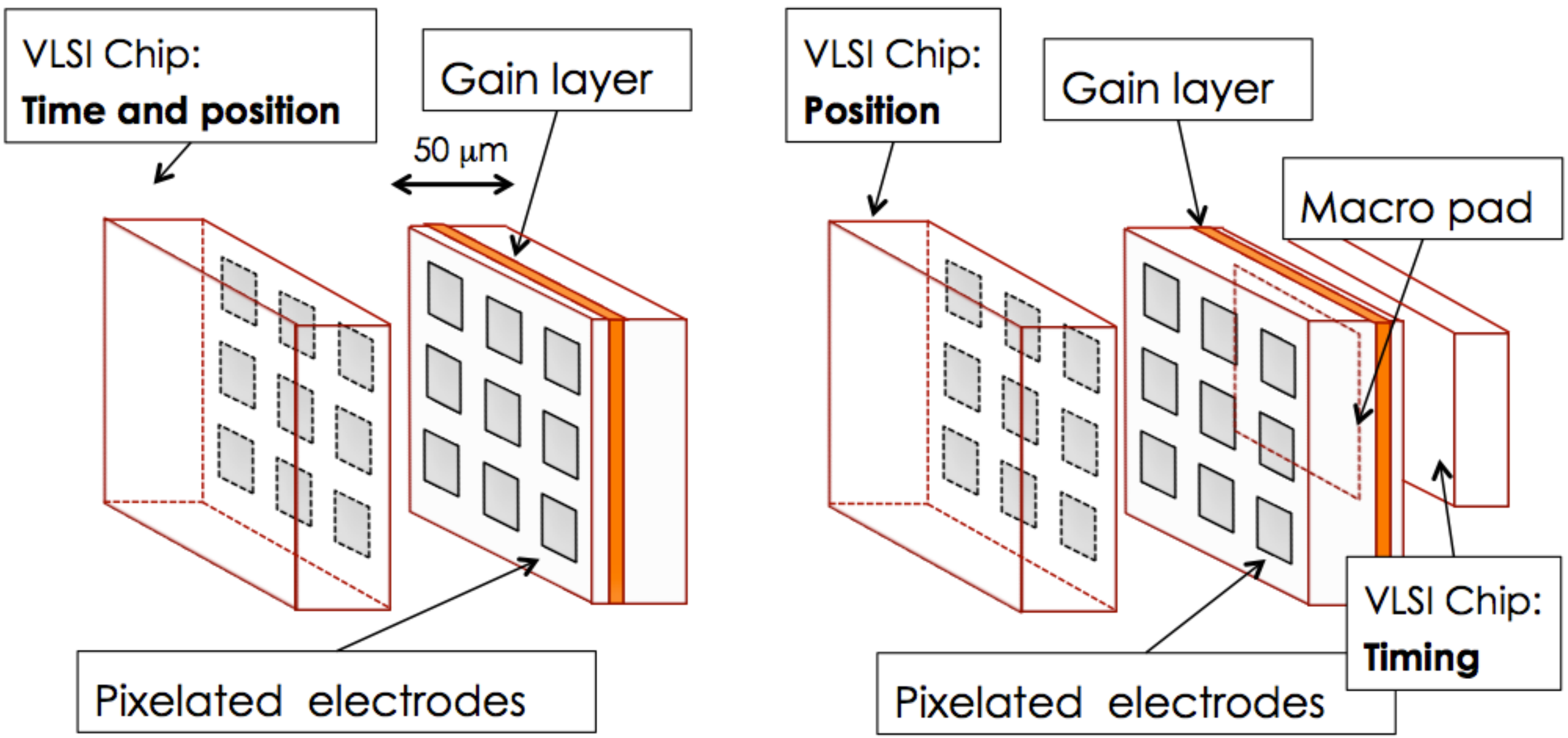
3) Segmentation: splitting gain and position measurements



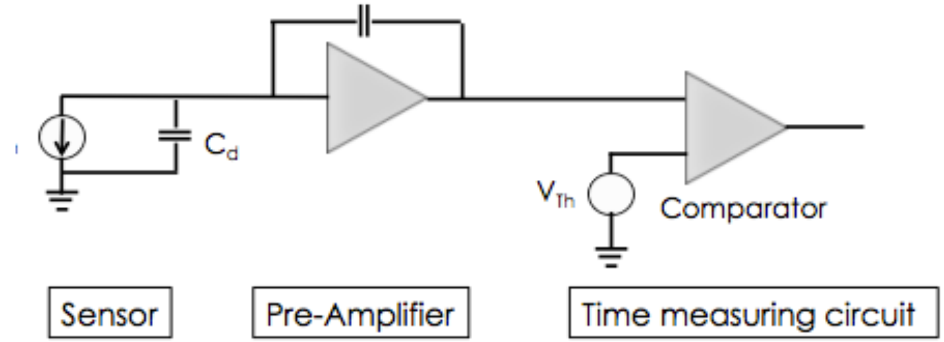
The ultimate time resolution will be obtained with a custom ASIC.

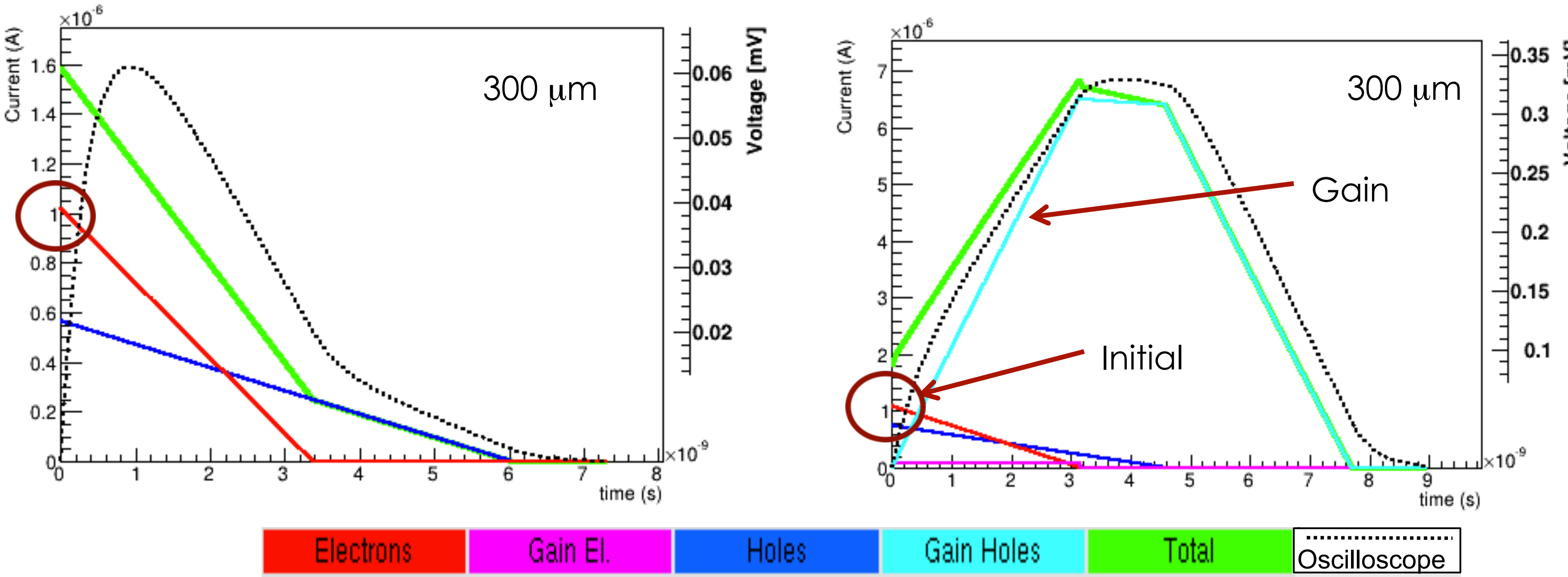
However we might split the position and the time measurements

Electronics

To fully exploit UFSDs, dedicated electronics needs to be designed.

The signal from UFSDs is different from that of traditional sensors





Simulated Weightfield2

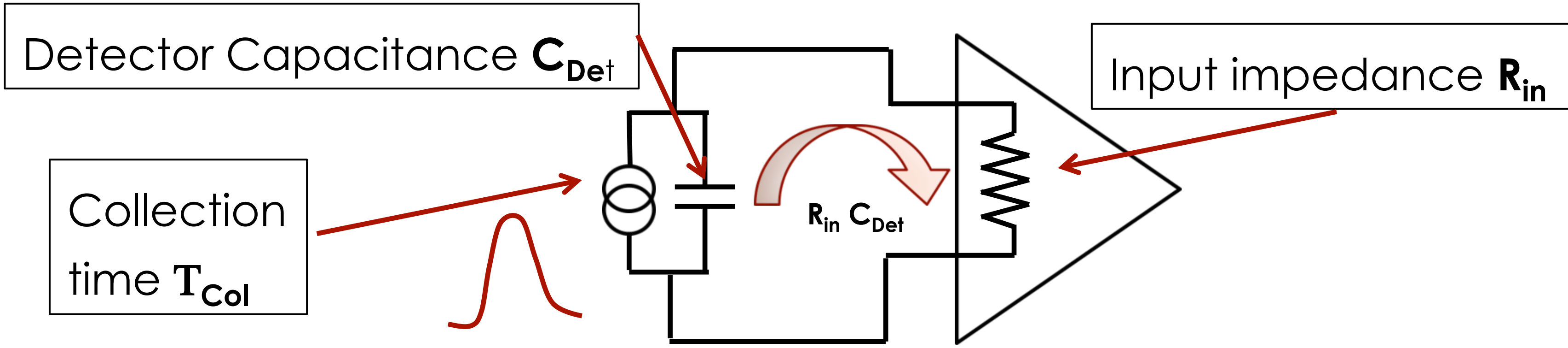
Pads with no gain

Charges generated uniquely by the incident particle

Pads with gain

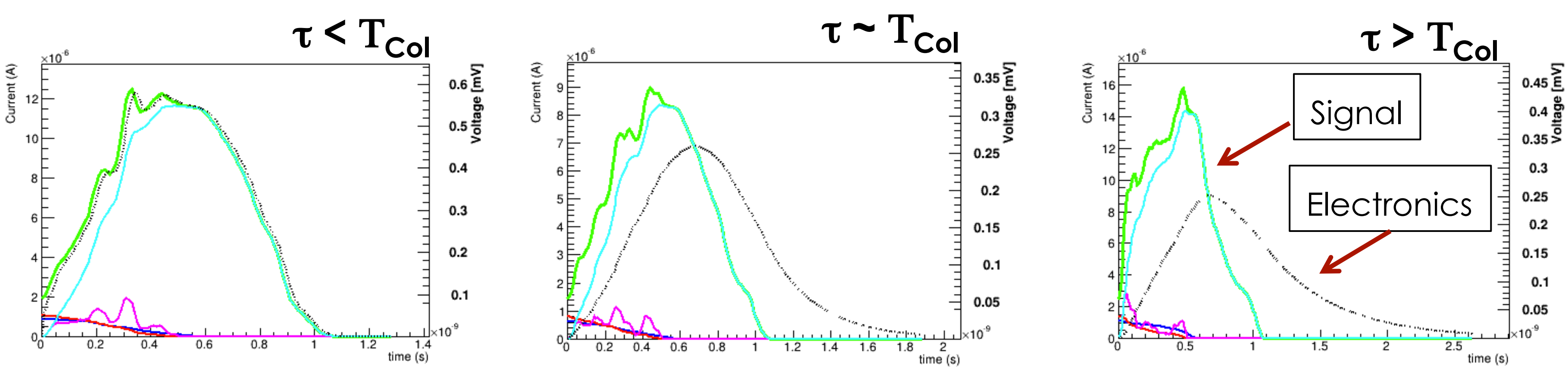
Current due to gain holes creates a longer and higher signal

Interplay of T_{Col} and $\tau = R_{in}\, C_{Det}$



There are two time constants at play:

- T_{Col} : the signal collection time (or equivalently the rise time)
- $\tau = R_{in}\, C_{Det}$: the time needed for the charge to move to the electronics

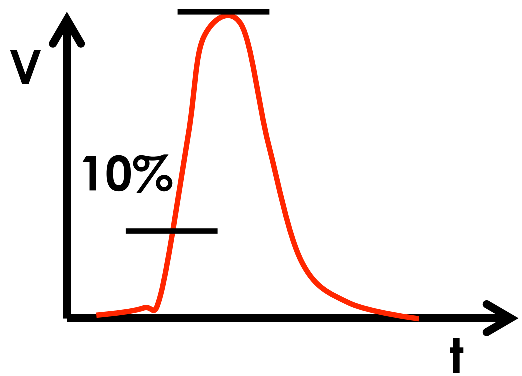


τ/T_{Col} increases ➔ dV/dt decreases

➔ Smoother current

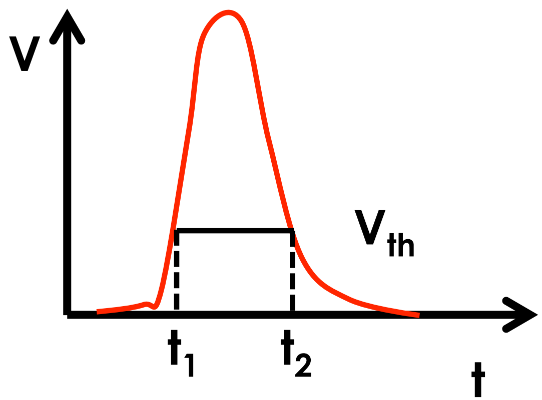
Need to find the optimum balance

What is the best "time measuring" circuit?



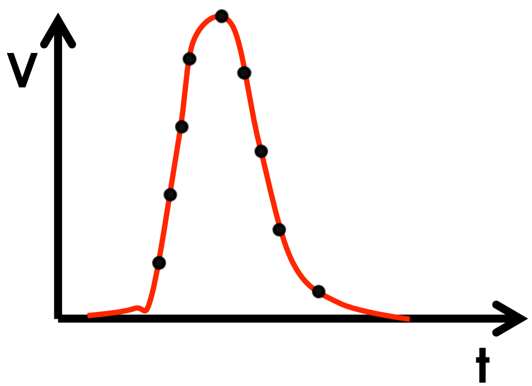
Constant Fraction Discriminator

The time is set when a fixed fraction of the amplitude is reached



Time over Threshold

The amount of time over the threshold is used to correct for time walk

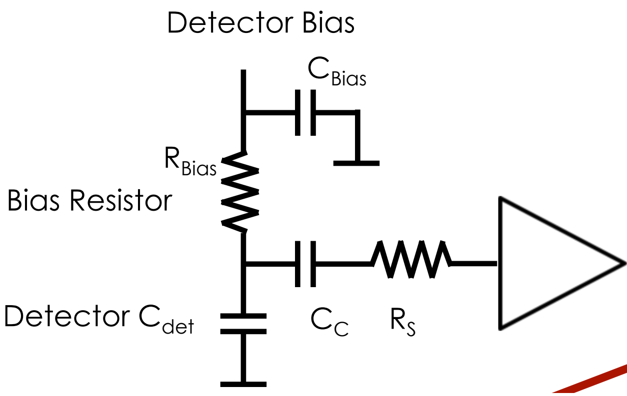


Multiple sampling

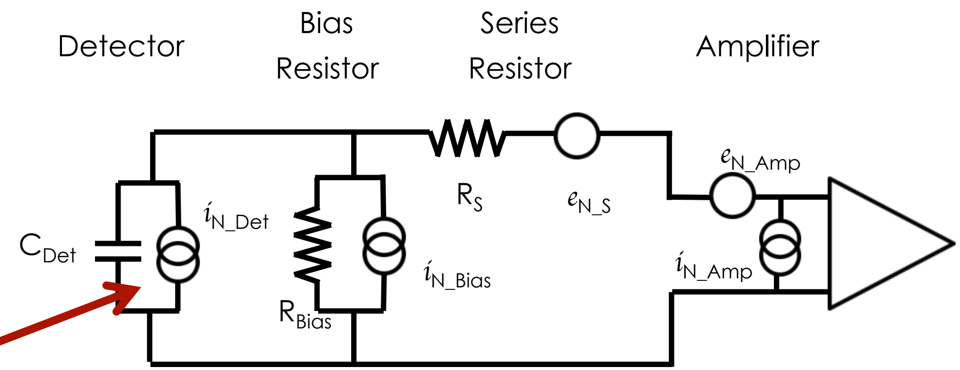
Most accurate method, needs a lot of computing power.

Noise - I

Real life



Noise Model



This term, the detector current shot noise, depends on the gain

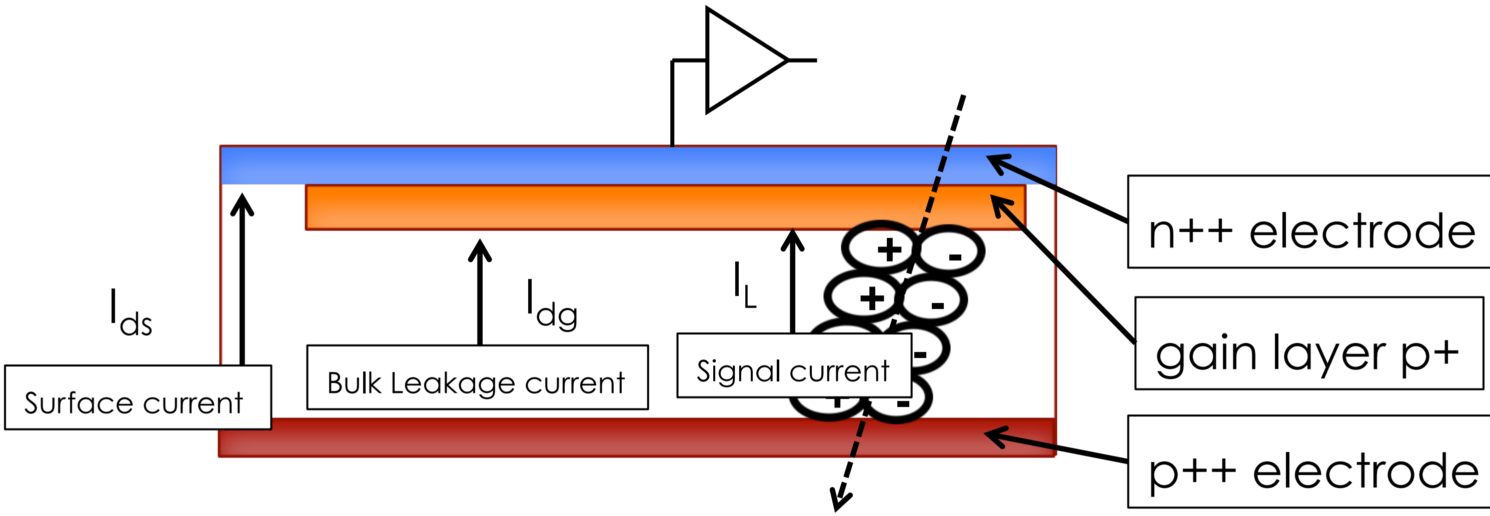
$$Q_n^2 = \left(2eI_{Det} + \frac{4kT}{R_{Bias}} + i^2_{N\_Amp}\right)F_i T_s + \left(4kTR_s + e^2_{N\_Amp}\right)F_v \frac{C^2_{Det}}{T_S} + F_{vf} A_f C^2_{Det}$$

$2eI_{Det}$ * Gain

low gain!

This term dominates for short shaping time

Details of shot noise in LGAD - APD



$$i^2_{Shot} = 2eI_{Det} = 2e\left[I_{Surface} + (I_{Bulk} + I_{Signal})M^2F\right]$$

Correction factor to the standard Shot noise, due to the noise of the multiplication mechanism

$$F = Mk + \left(2 - \frac{1}{M}\right)(1-k)$$

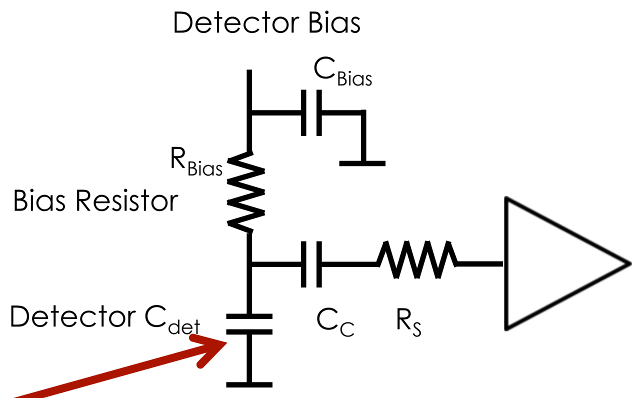
$$F \sim M^x$$

k = e/h ionization rate
x = excess noise index
M = gain

$$F = \frac{\langle M^2 \rangle}{\langle M \rangle^2} \Rightarrow \langle M^2 \rangle = \langle M \rangle^2 F$$

Noise - II

Real life



$$ENF = kG + \left(2 - \frac{1}{G}\right)(1-k)$$

k = ratio h/e gain

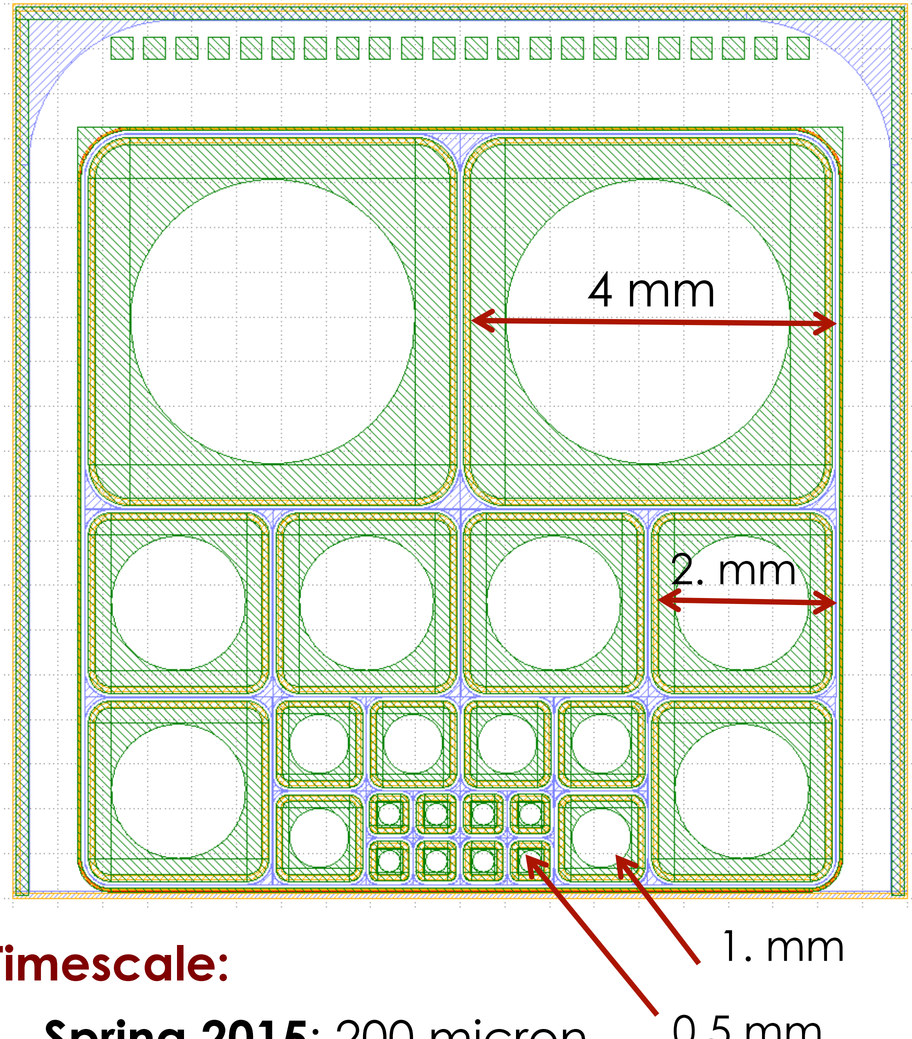
NOISE DUE TO GAIN:

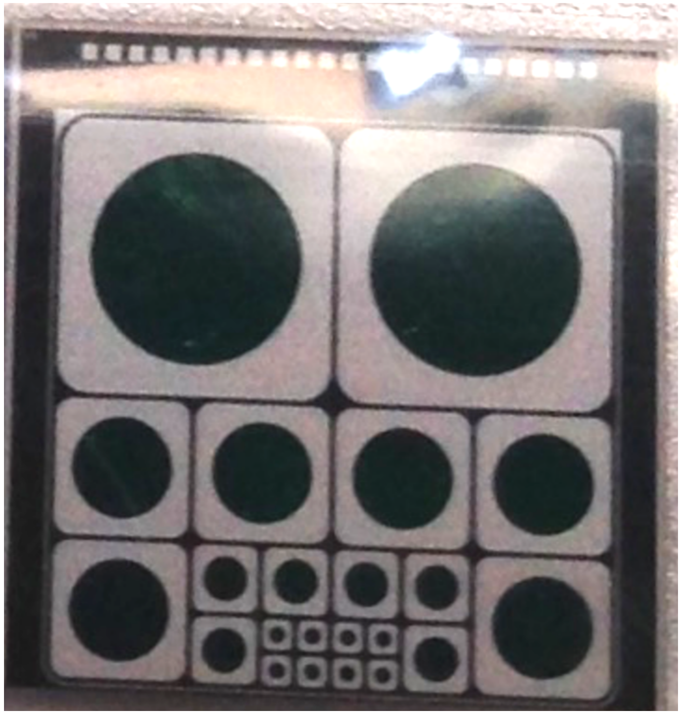
Excess noise factor:

low gain, very small k

Low leakage current and low gain (~ 10) together with short shaping time are necessary to keep the noise down.

Next CNM productions





These new productions will allow a detailed exploration of the UFSD timing capabilities, including border effects between pads, and distance from the sensor edge.

Timescale:

- **Spring 2015**: 200 micron
- **Summer 2015**: 100 micron
- **Summer 2015**: 50 micron

Next Steps

1. Wafer Production
   200 micron thick sensors by **Spring-2015**
   100 and 50 micron thick sensors by **Summer 2015.**

2. Production of UFSD doped with Gallium instead of Boron.

3. Study of reversed-UFSD started for the production of pixelated UFSD sensors (FBK, Trento).

4. UFSD are included in the CMS TDR CT-PPS as a solution for forward proton tagging

5. Use of UFSD in beam monitoring for hadron beam. INFN patent and work on-going

6. Interest in UFSD for 4D tracking at high luminosity

7. Testbeam analyses just started. Results coming soon…

UFSD – Summary

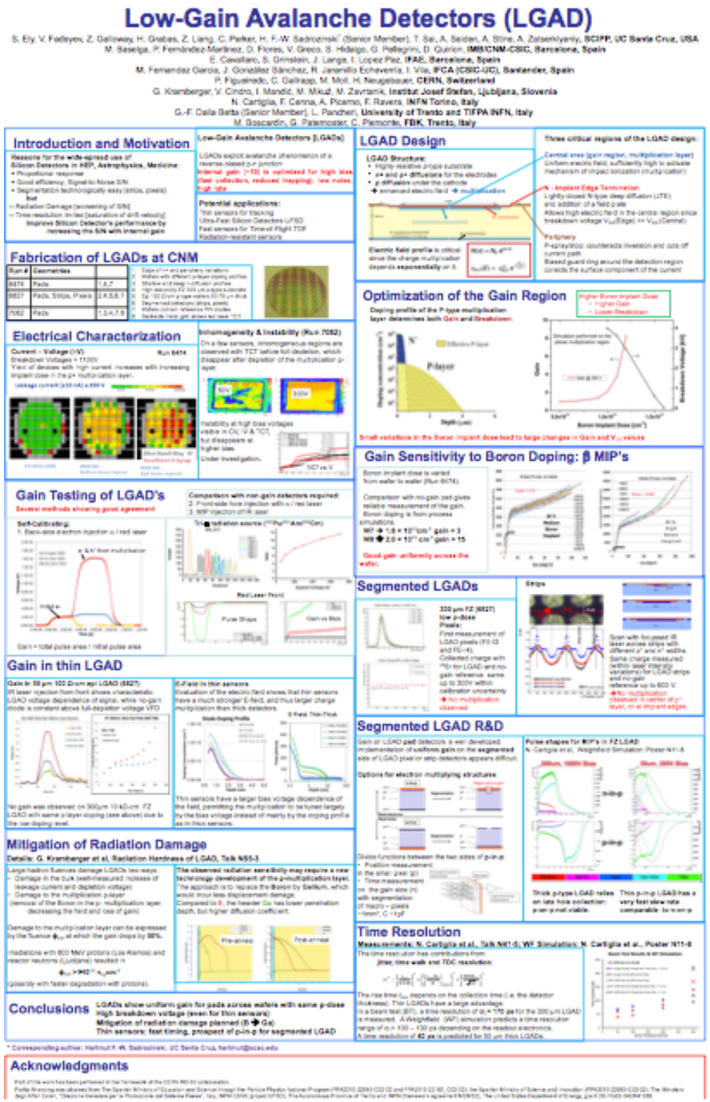
We are just starting to understand the timing capability of UFSD

- Low-gain avalanche diodes (LGAD) offer silicon sensors with an enhanced signal amplitude: UFSD are LGAD detectors optimized for timing resolution.
- Several options under studies to obtain concurrently excellent space and time resolutions.

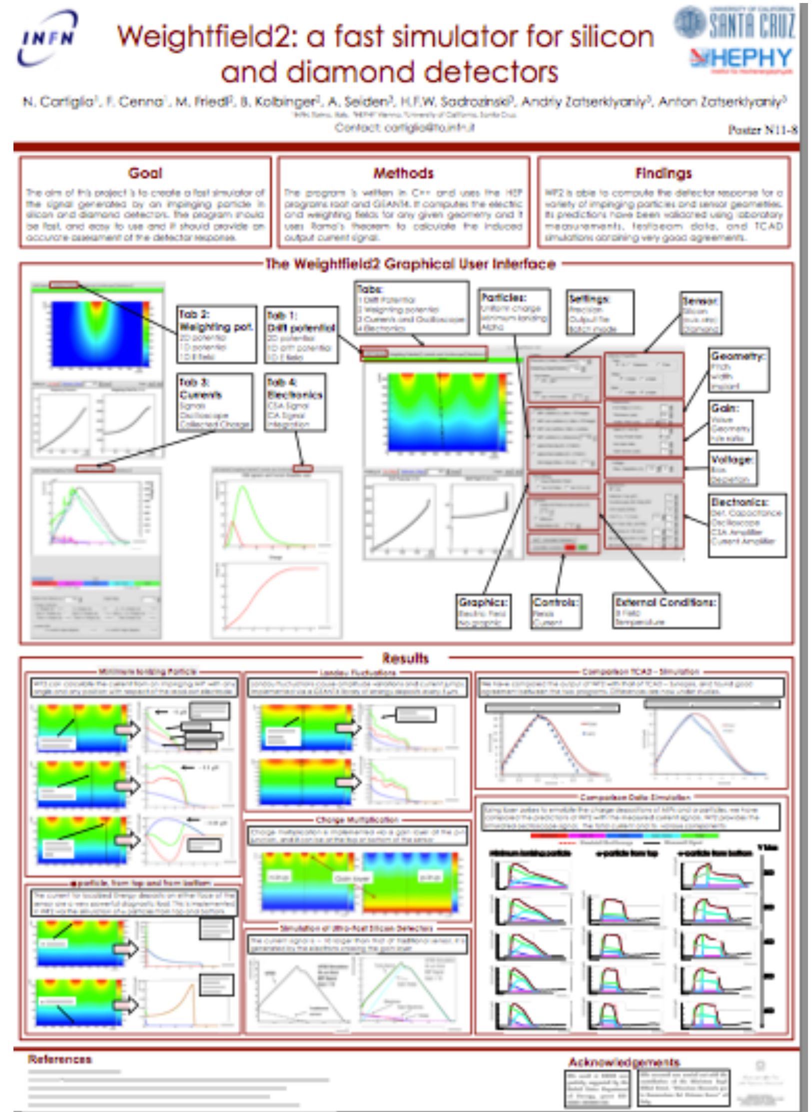
- We developed a program, **Weightfield2** to simulate the behaviors of LGAD and optimized them for fast timing (available at http://personalpages.to.infn.it/~cartigli/Weightfield2.0/)

Timescale: 1 year to asses UFSD timing capabilities

Presented at IEEE, oral and posters, presentations



Poster Session IEEE N26-13



Poster Session IEEE N11-8

Additional references

Several talks at the 22nd, 23rd and 24th RD50 Workshops:

23rd RD50: https://indico.cern.ch/event/265941/other-view?view=standard
22nd RD50: http://panda.unm.edu/RD50_Workshop/

10th Trento Workshop, Trento, Feb 2015.

9Th Trento Workshop, Genova, Feb 2014.

F. Cenna "**Simulation of Ultra-Fast Silicon Detectors**"

N. Cartiglia "**Timing capabilities of Ultra-Fast Silicon Detector**"

Papers:

[1] N. Cartiglia, Ultra-Fast Silicon Detector, 13th Topical Seminar on Innovative Particle and Radiation Detectors (IPRD13), 2014 JINST 9 C02001, http://arxiv.org/abs/1312.1080

[2] H.F.-W. Sadrozinski, N. Cartiglia et al., Sensors for ultra-fast silicon detectors, Proceedings "Hiroshima" Symposium HSTD9, DOI: 10.1016/j.nima.2014.05.006 (2014).

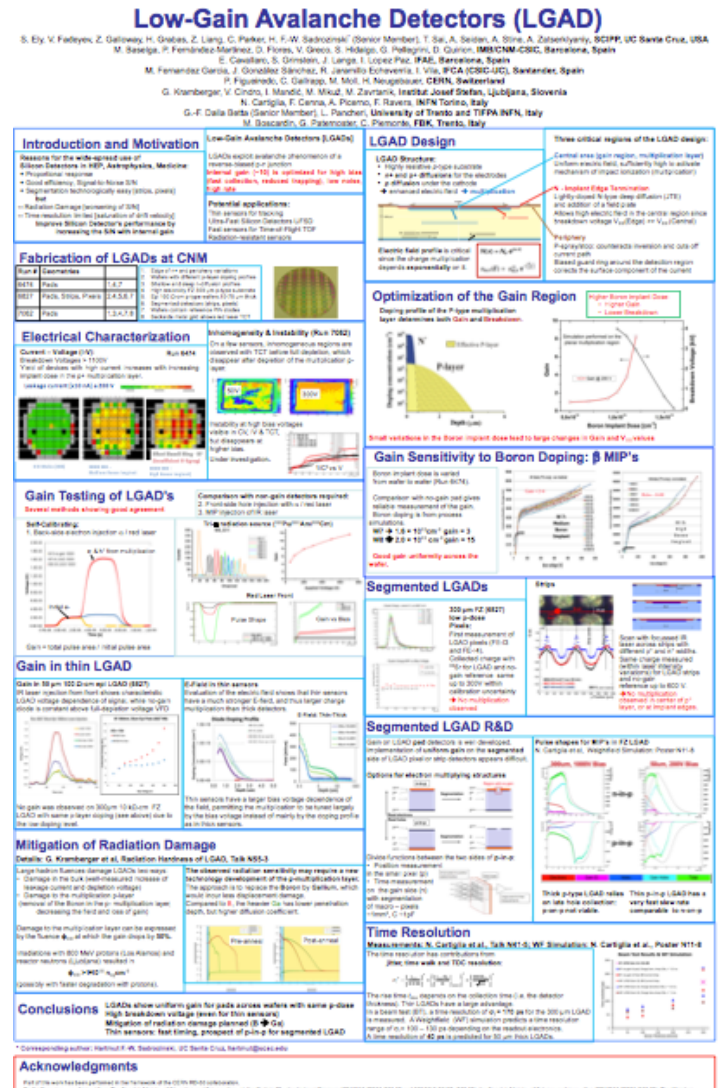
Backup

The "Low-Gain Avalanche Detector" project

Is it possible to manufacture a silicon detector that looks like a normal pixel or strip sensor, but

with a much larger signal (RD50)?

- 730 e/h pair per micron instead of 73 e/h
- Finely segmented
- Radiation hard
- No dead time
- Very low noise (low shot noise)
- No cross talk



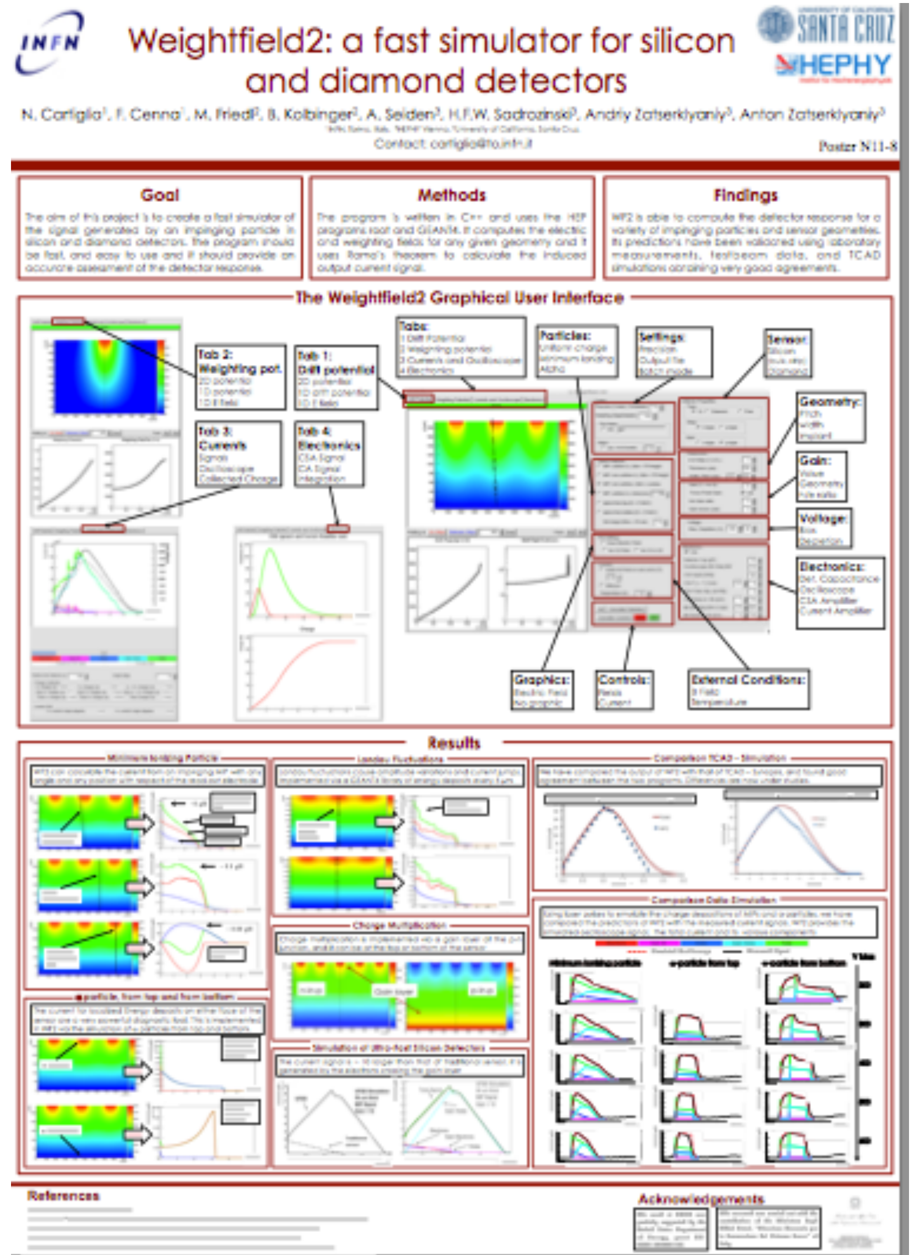
Poster Session IEEE N26-13

How can we progress? Need simulation

We developed a full simulation program to optimize the sensor design, WeightField2, (http://cern.ch/weightfield2)

It includes:

- Custom Geometry
- Calculation of drift field and weighting field
- Currents signal via Ramo's Theorem
- Gain
- Diffusion
- Temperature effect
- Non-uniform deposition
- Electronics

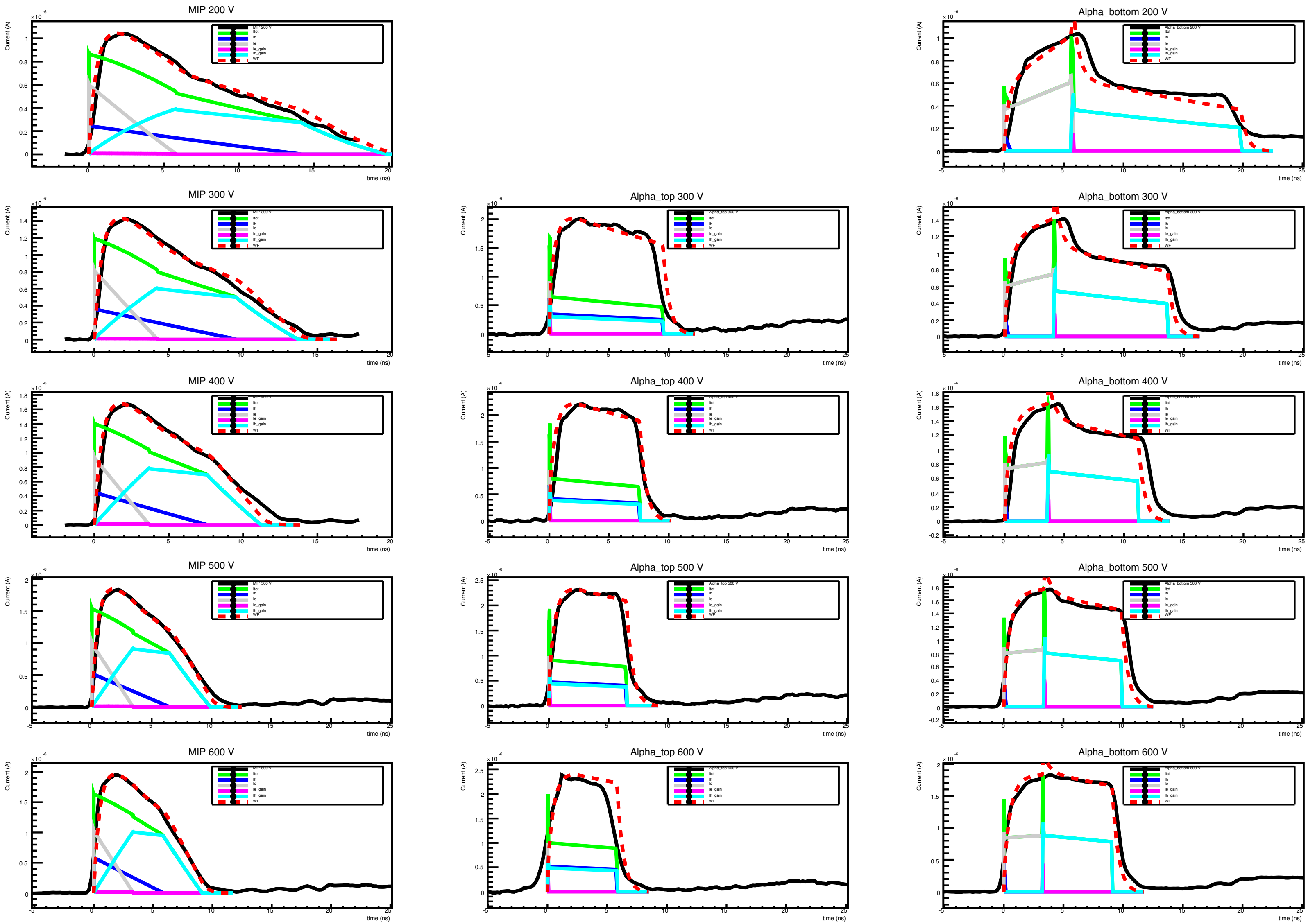


Poster Session IEEE N11-8

Comparison Data Simulation

Nicolo Cartiglia, INFN, Torino - UFSD; DESY , 20 March 2015

MIP | **Alpha from Top** | **Alpha from bottom** | **V bias**



200

300

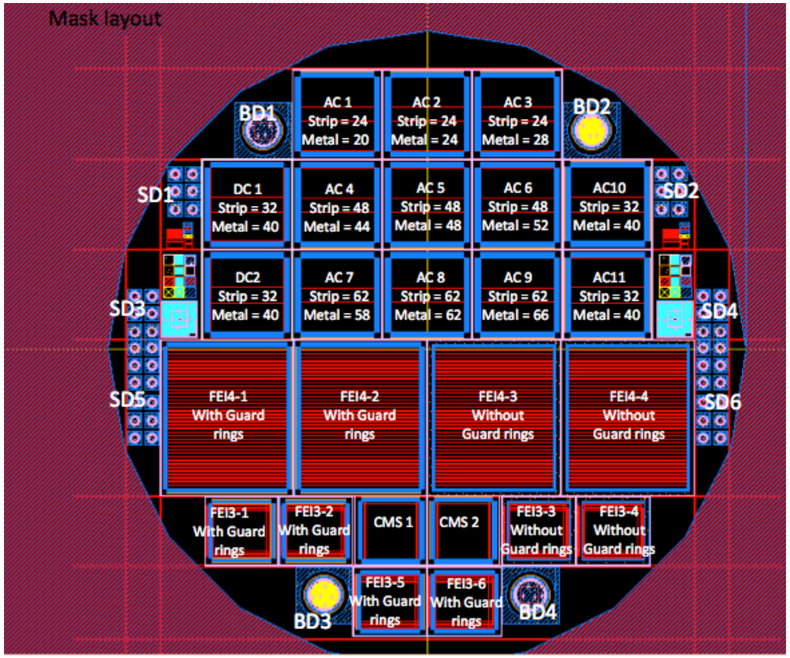
400

500

600

CNM LGADs mask

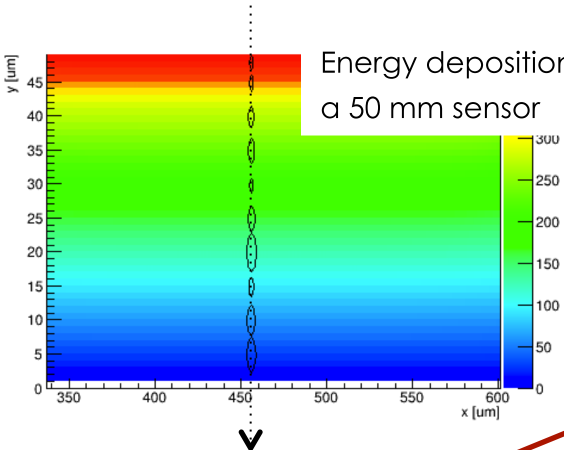
CNM, within the RD50 project, manufactured several runs of LGAD, trying a large variety of geometries and designs



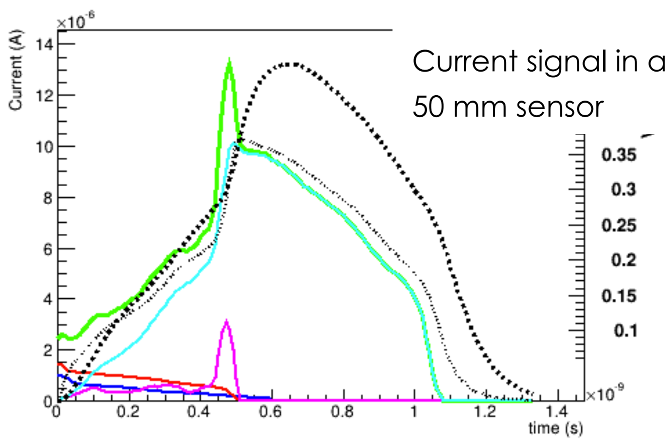
This implant controls the value of the gain

Wafer Number	P-layer Implant (E = 100 keV)	Substrate features	Expected Gain
1-2	1.6×10^{13} cm^{-2}	HRP 300 (FZ; ρ >10 KΩ ·cm; <100>; T = 300±10 µm)	2 – 3
3-4	2.0×10^{13} cm^{-2}	HRP 300 (FZ; ρ >10 KΩ ·cm; <100>; T = 300±10 µm)	8 – 10
5-6	2.2×10^{13} cm^{-2}	HRP 300 (FZ; ρ >10 KΩ ·cm; <100>; T = 300±10 µm)	15
7	(---) PiN Wafer	HRP 300 (FZ; ρ >10 KΩ ·cm; <100>; T = 300±10 µm)	No Gain

Electronics: What is the best pre-amp choice?

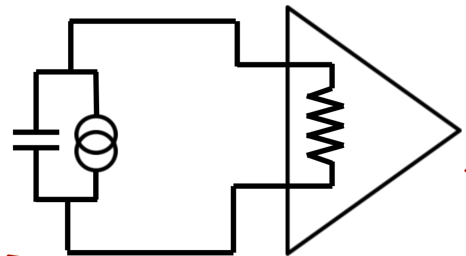


Energy deposition in a 50 mm sensor

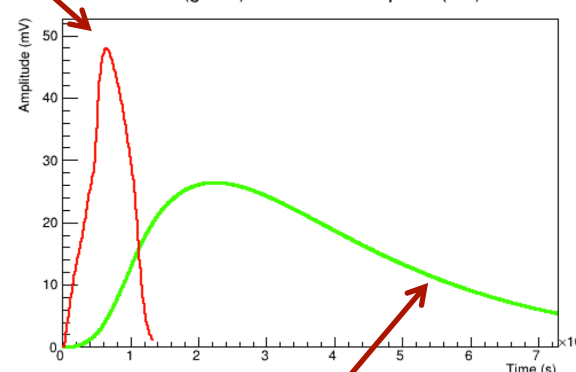


Current signal in a 50 mm sensor

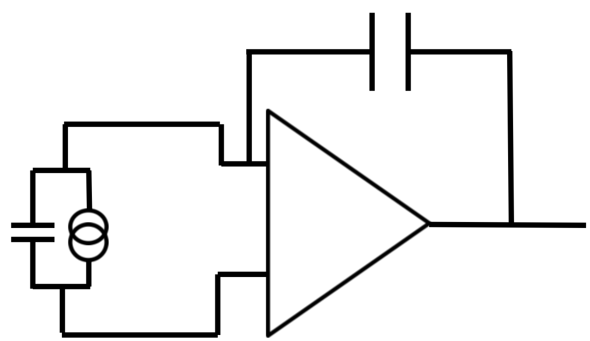
Current Amplifier



- Fast slew rate
- Higher noise
- Sensitive to Landau bumps

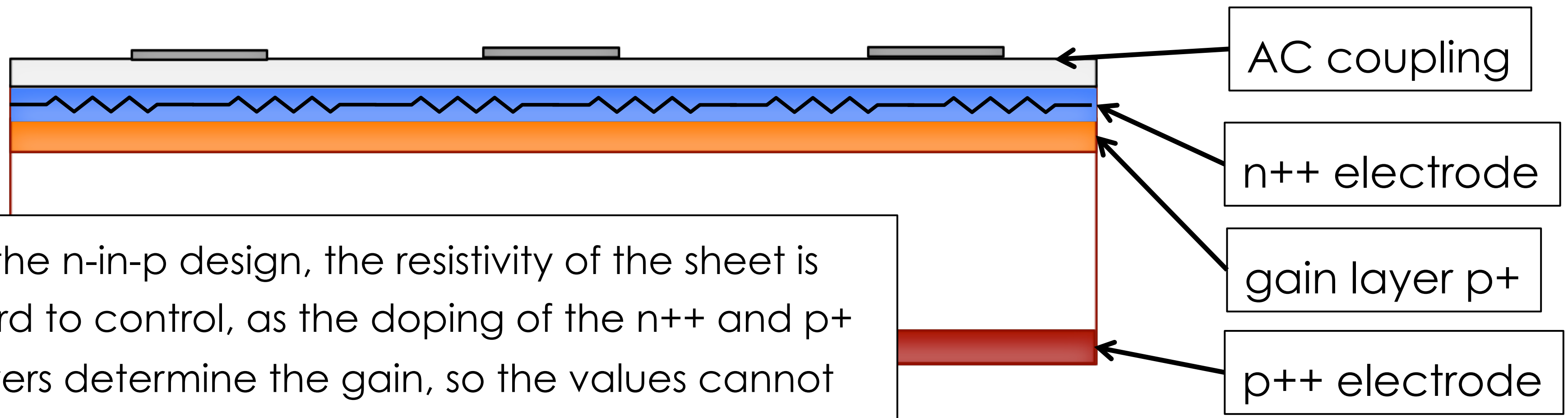


Integrating Amplifier

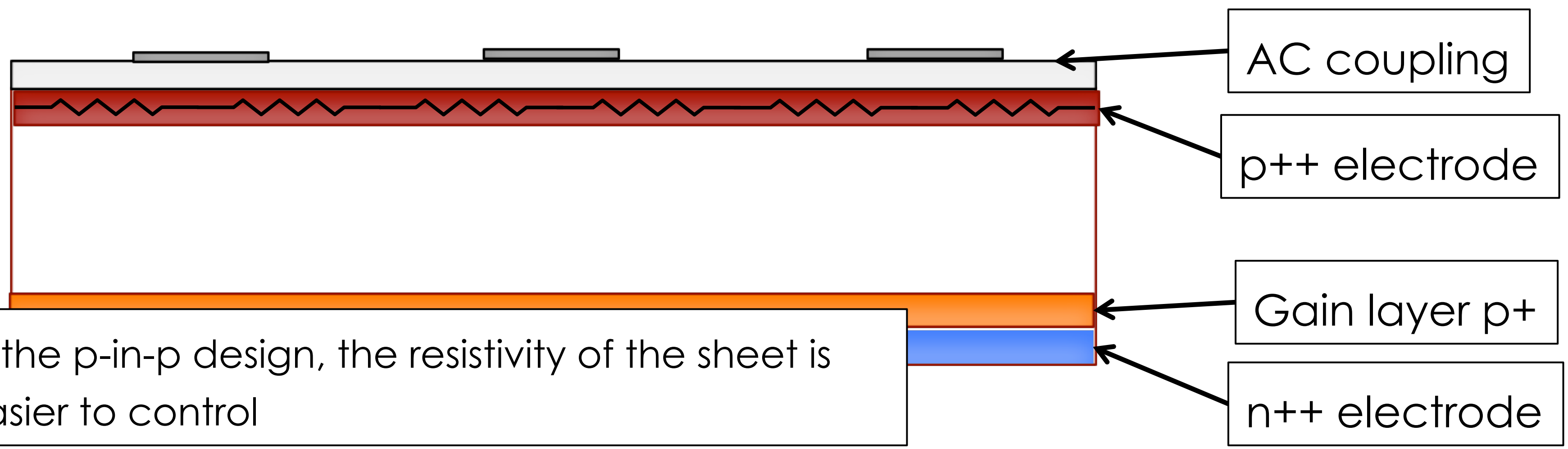


- Slower slew rate
- Quieter
- Integration helps the signal smoothing

Details of AC coupling - II



In the n-in-p design, the resistivity of the sheet is hard to control, as the doping of the n++ and p+ layers determine the gain, so the values cannot be chosen as we like.



In the p-in-p design, the resistivity of the sheet is easier to control

Drift Velocity

$$i \propto q v E_w$$

➔ Highest possible E field to saturate velocity
➔ Highest possible resistivity for velocity uniformity

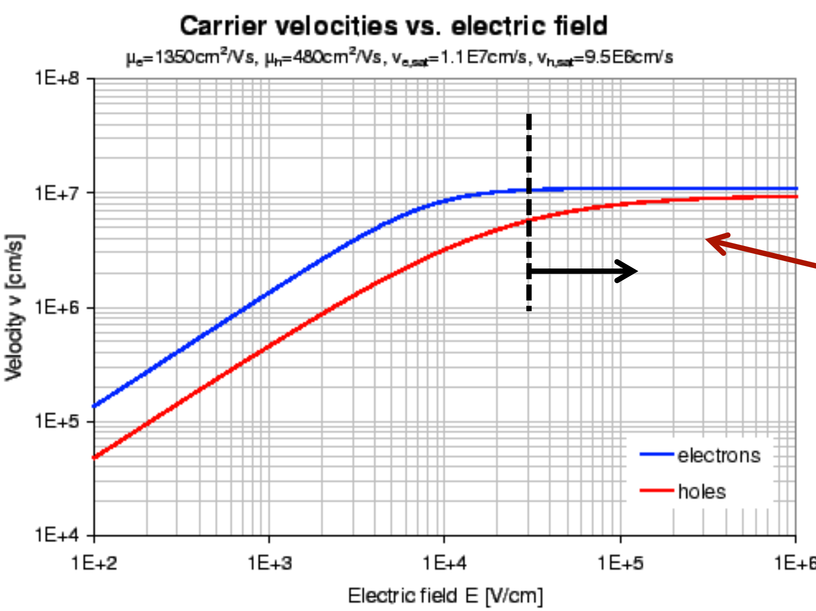


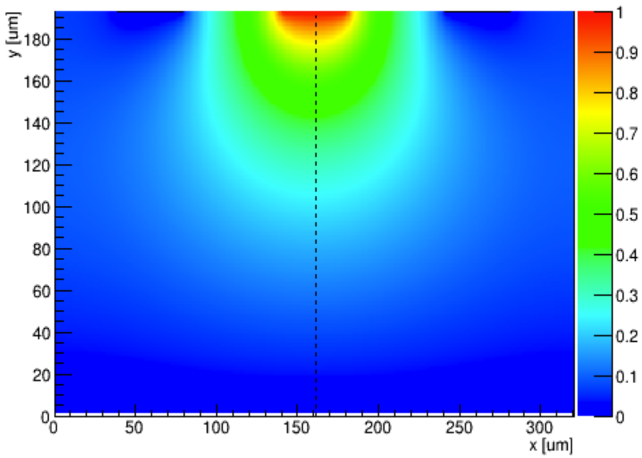
Figure: Electron and hole velocities vs. the electric field strength in silicon.

We want to operate in this regime

Weighting Field: coupling the charge to the electrode

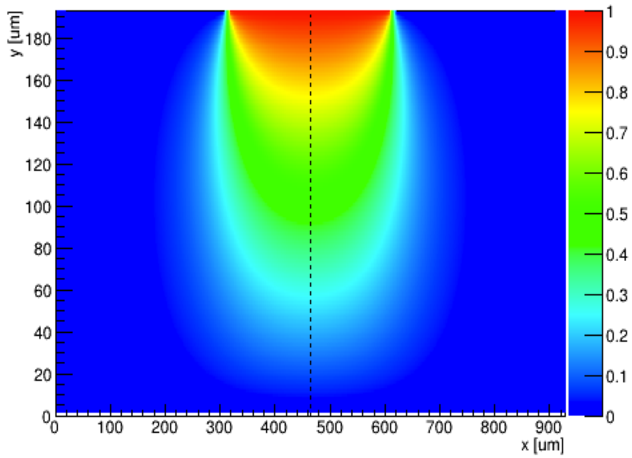
$$i \propto q v E_w$$

Strip: 100 μm pitch, 40 μm width



Bad: almost no coupling away from the electrode

Pixel: 300 μm pitch, 290 μm width



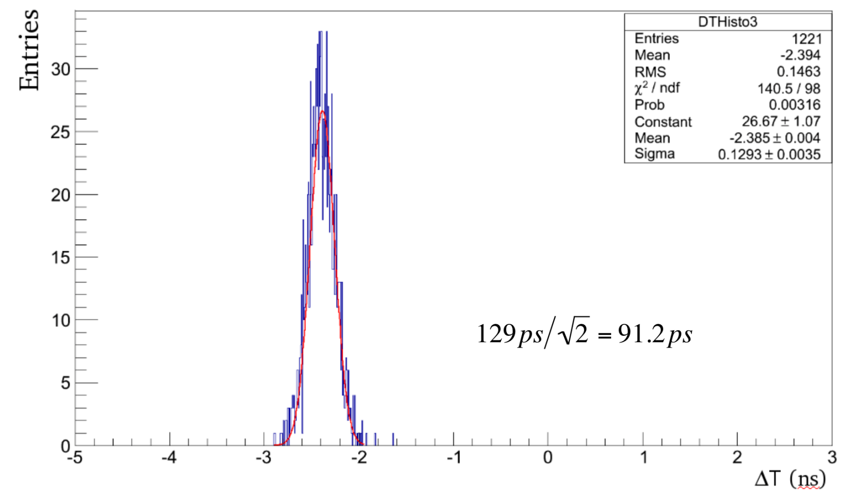
Good: strong coupling almost all the way to the backplane

The weighting field needs to be as uniform as possible, so that the coupling is always the same, regardless of the position of the charge

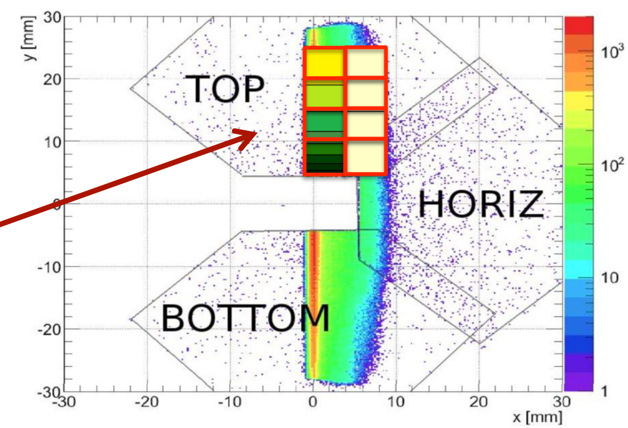
The Diamond approach - II

TOTEM collaboration: couple diamond detector with a tailored front-end and a full digitizing readout (SAMPIC, Switching Capacitor Sampler)

Excellent results at a very recent testbeam with ~ 4.5 x 4.5 mm^2 detectors



The result allows TOTEM to introduce timing measurement is their Roman Pot set-up:
Vertical top pots used for timing



Noise for Gain = 1 and Gain = 10

Let's use the following parameterization (Spieler, Semiconductor Detector, pag 35):

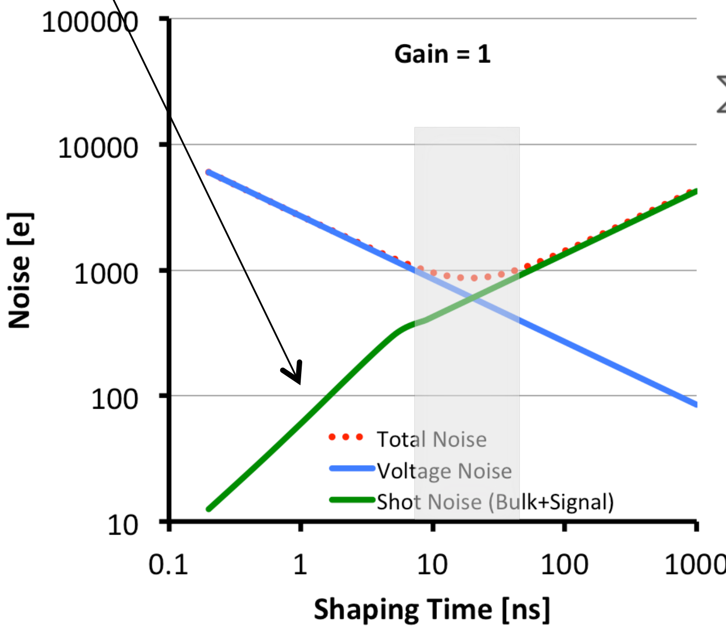
$$Q_n^2 = 12\,[\frac{e^2}{nA*ns}](I_{Bulk}+I_{Signal})M^{2+x}\tau + 3.6*10^4[\frac{e^2 ns}{pF^2 nV^2/Hz}]e_{N\_Amp}^2\frac{C_{Det}^2}{\tau}$$

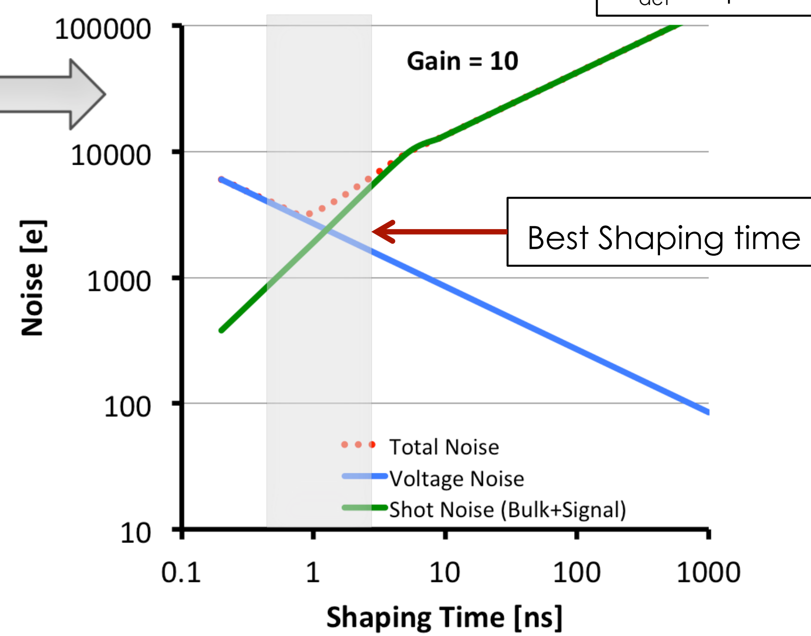
Shot Noise | Voltage Noise

Current noise very important at small shaping time

I_{bulk} = 1nA
I_{signal} = 300 nA * 5 ns
x = 1
C_{det} = 1 pF

Effect of the gain





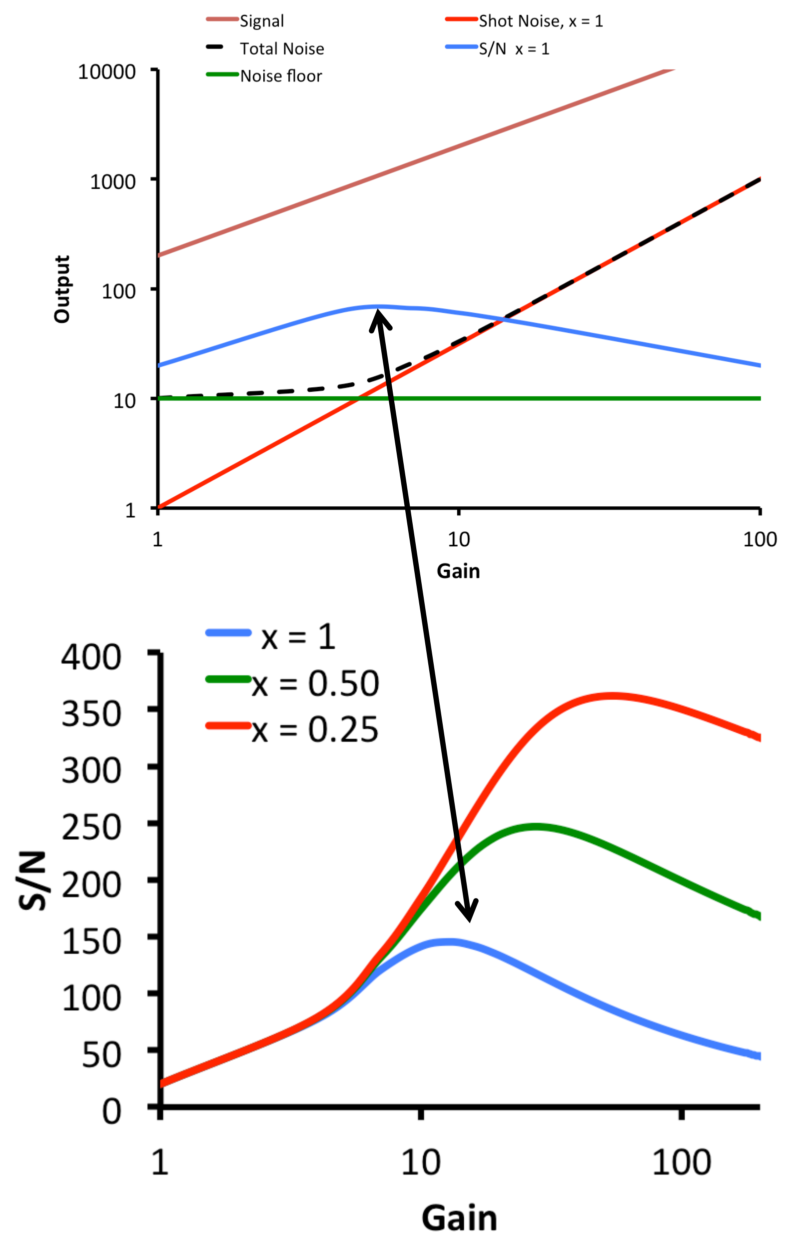
The minimum noise value is pushed higher and to a much shorter shaping time:

1000e- at 20 ns with Gain = 1 → 3000e- @ 1 ns with Gain = 10

→LGADs need very short shaping time ←

LGAD Optimum S/N: numbers

The noise increases faster than then signal: the ratio S/N becomes worse at higher gain.
➔There is an Optimum Gain value ➔



Let's consider the following situation:

- Signal = 20k e-
- Shaping time 1 ns
- Voltage Noise = 1k e-
- Shot Noise (G = 1) = 10 e- l
- Excess Noise Factor M^x x = 0.25, 0.5,1

Summary

1) For a given ENF, there is an optimum gain
2) The optimum gain is a function of the excess noise exponent x: higher x values cause lower optimum gains
3) Higher optimum gains require shorter shaping time